

# WIDEBAND, LOW-NOISE, LOW-DISTORTION, FULLY-DIFFERENTIAL AMPLIFIER

Check for Samples: [THS4513](#)

## FEATURES

- Fully-Differential Architecture
- Centered Input Common-Mode Range
- Minimum Gain of 1 V/V (0 dB)
- Bandwidth: 1600 MHz
- Slew Rate: 5100 V/ $\mu$ s
- 1% Settling Time: 2.9 ns
- HD<sub>2</sub>: –75 dBc at 70 MHz
- HD<sub>3</sub>: –86 dBc at 70 MHz
- OIP<sub>2</sub>: 77 dBm at 70 MHz
- OIP<sub>3</sub>: 42 dBm at 70 MHz
- Input Voltage Noise: 2.2 nV/ $\sqrt{\text{Hz}}$  ( $f > 10$  MHz)
- Noise Figure: 19.8 dB
- Output Common-Mode Control
- Power Supply:
  - Voltage: 3 V ( $\pm 1.5$  V) to 5 V ( $\pm 2.5$  V)
  - Current: 37.7 mA
- Power-Down Capability: 0.65 mA

## APPLICATIONS

- 5-V Data Acquisition Systems, High Linearity ADC Amplifier
- Wireless Communication
- Medical Imaging
- Test and Measurement

## RELATED PRODUCTS

DEVICE	MIN. GAIN	COMMON-MODE RANGE OF INPUT <sup>(1)</sup>
<a href="#">THS4508</a>	6 dB	–0.3 V to 2.3 V
<a href="#">THS4509</a>	6 dB	1.1 V to 3.9 V
<a href="#">THS4511</a>	0 dB	–0.3 V to 2.3 V
<a href="#">THS4513</a>	0 dB	1.1 V to 3.9 V

1. Assumes a 5-V single-ended power supply.

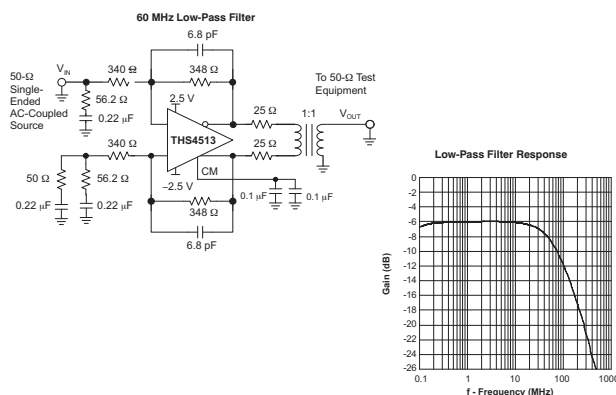
## DESCRIPTION

The THS4513 is a wideband, fully-differential op amp designed for 3.3-V to 5-V data acquisition systems. It has very low noise at 2.2 nV/ $\sqrt{\text{Hz}}$ , and extremely low harmonic distortion of –75 dBc HD<sub>2</sub> and –86 dBc HD<sub>3</sub> at 70 MHz with 2-V<sub>PP</sub> output, G = 0 dB, and 200- $\Omega$  load. Slew rate is very high at 5100 V/ $\mu$ s and with settling time of 2.9 ns to 1% (2-V step), it is ideal for pulsed applications. It is designed for a minimum gain of 0 dB.

To allow for dc-coupling to analog-to-digital converters (ADCs), its unique output common-mode control circuit maintains the output common-mode voltage within 5-mV offset (typ) from the set voltage, when set within 0.5 V of midsupply, with less than 4-mV differential offset voltage. The common-mode set point is set to midsupply by internal circuitry, which may be overdriven from an external source.

The input and output are optimized for best performance with their common-mode voltages set to midsupply. Along with high performance at low power-supply voltage, this design makes it ideal for extremely high-performance, single-supply 5-V data acquisition systems.

The THS4513 is offered in a quad, leadless QFN-16 package (RGT), and is characterized for operation over the full industrial temperature range from –40°C to +85°C.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

PowerPAD is a trademark of Texas Instruments Incorporated.  
All other trademarks are the property of their respective owners.

PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of the Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.

Copyright © 2005–2013, Texas Instruments Incorporated



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

### PACKAGING/ORDERING INFORMATION<sup>(1)</sup>

TEMPERATURE	PACKAGED DEVICES	
	QUAD QFN <sup>(2)(3)</sup> (RGT-16)	SYMBOL
–40°C to +85°C	THS4513RGTT	—
	THS4513RGTR	

- (1) For the most current package and ordering information see the Package Option Addendum at the end of this document, or see the TI web site at [www.ti.com](http://www.ti.com).  
 (2) This package is available taped and reeled. The **R** suffix standard quantity is 3000. The **T** suffix standard quantity is 250.  
 (3) The exposed thermal pad is electrically isolated from all other pins.

### ABSOLUTE MAXIMUM RATINGS<sup>(1)</sup>

Over operating free-air temperature range, unless otherwise noted.

		UNIT
$V_{S-}$ to $V_{S+}$	Supply voltage	6 V
$V_I$	Input voltage	$\pm V_S$
$V_{ID}$	Differential input voltage	4 V
$I_O$	Output current <sup>(2)</sup>	200 mA
Continuous power dissipation		See <a href="#">Dissipation Ratings Table</a>
$T_J$	Maximum junction temperature	+150°C
$T_A$	Operating free-air temperature range	–40°C to +85°C
$T_{STG}$	Storage temperature range	–65°C to +150°C
ESD ratings	HBM	2000 V
	CDM	1500 V
	MM	100 V

- (1) Stresses above these ratings may cause permanent damage. Exposure to absolute maximum conditions for extended periods may degrade device reliability. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those specified is not implied.  
 (2) The THS4513 incorporates a (QFN) exposed thermal pad on the underside of the chip. This pad acts as a heatsink and must be connected to a thermally dissipative plane for proper power dissipation. Failure to do so may result in exceeding the maximum junction temperature which could permanently damage the device. See TI technical briefs [SLMA002](#) and [SLMA004](#) for more information about utilizing the QFN thermally-enhanced package.

### DISSIPATION RATINGS TABLE

PACKAGE	$\theta_{JC}$	$\theta_{JA}$	POWER RATING	
			$T_A \leq +25^\circ\text{C}$	$T_A = +85^\circ\text{C}$
RGT (16)	2.4°C/W	39.5°C/W	2.3 W	225 mW

**ELECTRICAL CHARACTERISTICS:  $V_{S+} - V_{S-} = 5\text{ V}$** 

Test conditions at  $V_{S+} = 2.5\text{ V}$ ,  $V_{S-} = -2.5\text{ V}$ ,  $G = 0\text{ dB}$ ,  $\text{CM} = \text{open}$ ,  $V_O = 2\text{ V}_{PP}$ ,  $R_F = 348\ \Omega$ ,  $R_L = 200\text{-}\Omega$  differential,  $T_A = +25^\circ\text{C}$ , single-ended input, differential output, and input and output referenced to midsupply, unless otherwise noted.

PARAMETER	TEST CONDITIONS		MIN	TYP	MAX	UNIT	TEST LEVEL <sup>(1)</sup>
AC PERFORMANCE							
Small-signal bandwidth	G = 0 dB, V <sub>O</sub> = 100 mV <sub>PP</sub>			1.6		GHz	C
	G = 6 dB, V <sub>O</sub> = 100 mV <sub>PP</sub>			1.4		GHz	
Gain-bandwidth product	G = 6 dB			2.8		GHz	
Bandwidth for 0-dB flatness	G = 0 dB, V <sub>O</sub> = 2 V <sub>PP</sub>			150		MHz	
	G = 6 dB, V <sub>O</sub> = 2 V <sub>PP</sub>			700			
Large-signal bandwidth	G = 0 dB, V <sub>O</sub> = 2 V <sub>PP</sub>			1.4		GHz	
Slew rate (differential)	2-V step			5100		V/μs	
Rise time fall time				0.5		ns	
				0.5			
Settling time to 1%				2.9			
Settling time to 0.1%				16			
2nd-order harmonic distortion	f = 10 MHz			−110		dBc	
	f = 50 MHz			−80			
	f = 100 MHz			−66			
3rd-order harmonic distortion	f = 10 MHz			−108		dBc	
	f = 50 MHz			−94			
	f = 100 MHz			−81			
2nd-order intermodulation distortion	V <sub>O</sub> = 2 V <sub>PP</sub> envelope, 200-kHz tone spacing, R <sub>L</sub> = 100 Ω	f <sub>C</sub> = 70 MHz		−78		dBc	
		f <sub>C</sub> = 140 MHz		−55			
3rd-order intermodulation distortion		f <sub>C</sub> = 70 MHz		−88			
		f <sub>C</sub> = 140 MHz		−72			
2nd-order output intercept point	200-kHz tone spacing R <sub>L</sub> = 100 Ω	f <sub>C</sub> = 70 MHz		77		dBm	
		f <sub>C</sub> = 140 MHz		53			
3rd-order output intercept point		f <sub>C</sub> = 70 MHz		42			
		f <sub>C</sub> = 140 MHz		34			
1-dB compression point	f <sub>C</sub> = 70 MHz			12.2		dBm	
	f <sub>C</sub> = 140 MHz			10.8			
Noise figure	50-Ω system, 10 MHz, G = 6 dB			19.8		dB	
Input voltage noise	f > 10 MHz			2.2		nV/√Hz	
Input current noise	f > 10 MHz			1.7		pA/√Hz	
DC PERFORMANCE							
Open-loop voltage gain (A <sub>OL</sub> )				63		dB	C
Input offset voltage	T <sub>A</sub> = +25°C			1	4	mV	A
	T <sub>A</sub> = −40°C to +85°C			1	5	mV	
Average offset voltage drift	T <sub>A</sub> = −40°C to +85°C			2.6		μV/°C	B
Input bias current	T <sub>A</sub> = +25°C			8	15.5	μA	A
	T <sub>A</sub> = −40°C to +85°C			8	18.5	μA	
Average bias current drift	T <sub>A</sub> = −40°C to +85°C			20		nA/°C	B
Input offset current	T <sub>A</sub> = +25°C			1.6	3.6	μA	A
	T <sub>A</sub> = −40°C to +85°C			1.6	7	μA	
Average offset current drift	T <sub>A</sub> = −40°C to +85°C			4		nA/°C	B

(1) Test levels: (A) 100% tested at  $+25^\circ\text{C}$ . Over-temperature limits by characterization and simulation. (B) Limits set by characterization and simulation. (C) Typical value only for information.

**ELECTRICAL CHARACTERISTICS:  $V_{S+} - V_{S-} = 5\text{ V}$  (continued)**

Test conditions at  $V_{S+} = 2.5\text{ V}$ ,  $V_{S-} = -2.5\text{ V}$ ,  $G = 0\text{ dB}$ ,  $\text{CM} = \text{open}$ ,  $V_O = 2\text{ V}_{PP}$ ,  $R_F = 348\ \Omega$ ,  $R_L = 200\text{-}\Omega$  differential,  $T_A = +25^\circ\text{C}$ , single-ended input, differential output, and input and output referenced to midsupply, unless otherwise noted.

PARAMETER	TEST CONDITIONS		MIN	TYP	MAX	UNIT	TEST LEVEL <sup>(1)</sup>
INPUT							
Common-mode input range high				1.4		V	B
Common-mode input range low				−1.4			
Common-mode rejection ratio				90			
Differential input impedance				1.3    1.8		MΩ    pF	C
Common-mode input impedance				1.0    2.3			
OUTPUT							
Maximum output voltage high	Each output with 100 Ω to midsupply	T <sub>A</sub> = +25°C	1.2	1.4		V	A
		T <sub>A</sub> = −40°C to +85°C	1.1	1.4			
Minimum output voltage low		T <sub>A</sub> = +25°C		−1.4	−1.2	V	
		T <sub>A</sub> = −40°C to +85°C		−1.4	−1.1		
Differential output voltage swing	T <sub>A</sub> = +25°C		4.8	5.6		V	
	T <sub>A</sub> = −40°C to +85°C		4.4	5.6		V	
Differential output current drive	R <sub>L</sub> = 10 Ω			96		mA	C
Output balance error	V <sub>O</sub> = 100 mV, f = 1 MHz			−52		dB	
Closed-loop output impedance	f = 1 MHz			0.3		Ω	
OUTPUT COMMON-MODE VOLTAGE CONTROL							
Small-signal bandwidth				250		MHz	C
Slew rate				110		V/μs	
Gain				1		V/V	
Output common-mode offset from CM input	−1 V < CM < 1 V			5		mV	
CM input bias current	−1 V < CM < 1 V			±40		μA	
CM input voltage range				−1.5 to 1.5		V	
CM input impedance				23    1		kΩ    pF	
CM default voltage				0		V	
POWER SUPPLY							
Specified operating voltage			3	5	5.5	V	C
Maximum quiescent current	T <sub>A</sub> = +25°C			37.7	40.9	mA	A
	T <sub>A</sub> = −40°C to +85°C			37.7	41.9		
Minimum quiescent current	T <sub>A</sub> = +25°C	34.5		37.7		mA	
	T <sub>A</sub> = −40°C to +85°C	33.5		37.7			
Power-supply rejection (±PSRR)				90		dB	C
POWER-DOWN							
Enable voltage threshold	Referenced to V <sub>S−</sub> , assured <i>on</i> above 2.1 V + V <sub>S−</sub>			> 2.1 + V <sub>S−</sub>		V	C
Disable voltage threshold	Assured <i>off</i> below 0.7 V + V <sub>S−</sub>			< 0.7 + V <sub>S−</sub>		V	
Power-down quiescent current	T <sub>A</sub> = +25°C			0.65	0.9	mA	A
	T <sub>A</sub> = −40°C to +85°C			0.65	1		
Input bias current	$\overline{\text{PD}}$ = V <sub>S−</sub>			100		μA	C
Input impedance				50    2		kΩ    pF	
Turn-on time delay	Measured to output on			55		ns	
Turn-off time delay	Measured to output off			10		μs	

**ELECTRICAL CHARACTERISTICS:  $V_{S+} - V_{S-} = 3\text{ V}$** 

Test conditions at  $V_{S+} = 1.5\text{ V}$ ,  $V_{S-} = -1.5\text{ V}$ ,  $G = 0\text{ dB}$ ,  $\text{CM} = \text{open}$ ,  $V_O = 1\text{ V}_{PP}$ ,  $R_F = 348\ \Omega$ ,  $R_L = 200\text{-}\Omega$  differential,  $T_A = +25^\circ\text{C}$ , single-ended input, differential output, and input and output referenced to midsupply, unless otherwise noted.

PARAMETER	TEST CONDITIONS		TYP	UNIT	TEST LEVEL <sup>(1)</sup>
AC PERFORMANCE					
Small-signal bandwidth	G = 0 dB, V <sub>O</sub> = 100 mV <sub>PP</sub>		1.6	GHz	C
	G = 6 dB, V <sub>O</sub> = 100 mV <sub>PP</sub>		1.3	GHz	
Gain-bandwidth product	G = 6 dB		2.6	GHz	
Bandwidth for 0-dB Flatness	G = 0 dB, V <sub>O</sub> = 1 V <sub>PP</sub>		135	MHz	
	G = 6 dB, V <sub>O</sub> = 1 V <sub>PP</sub>		450		
Large-signal bandwidth	G = 10 dB, V <sub>O</sub> = 1 V <sub>PP</sub>		1.4	GHz	
Slew rate (differential)	1-V step		2700	V/μs	
Rise time			0.25	ns	
Fall time			0.25		
Settling time to 1%			2.9		
Settling time to 0.1%			16		
2nd-order harmonic distortion			f = 10 MHz		
	f = 50 MHz		−86		
	f = 100 MHz		−60		
3rd-order harmonic distortion	f = 10 MHz		−83	dBc	
	f = 50 MHz		−61		
	f = 100 MHz		−49		
2nd-order intermodulation distortion	V <sub>O</sub> = 1 V <sub>PP</sub> 200-kHz tone spacing, R <sub>L</sub> = 100 Ω	f <sub>C</sub> = 70 MHz	−78	dBc	
		f <sub>C</sub> = 140 MHz	−55		
3rd-order intermodulation distortion		f <sub>C</sub> = 70 MHz	−82		
		f <sub>C</sub> = 140 MHz	−65		
2nd-order output intercept point	200-kHz tone spacing R <sub>L</sub> = 100 Ω	f <sub>C</sub> = 70 MHz	70.2	dBm	
		f <sub>C</sub> = 140 MHz	47		
3rd-order output intercept point		f <sub>C</sub> = 70 MHz	32.7		
		f <sub>C</sub> = 140 MHz	24.7		
1-dB compression point	f <sub>C</sub> = 70 MHz		3	dBm	
	f <sub>C</sub> = 140 MHz		2		
Noise figure	50-Ω system, 10 MHz, G = 6 dB		19.8	dB	
Input voltage noise	f > 10 MHz		3.3	nV/√Hz	
Input current noise	f > 10 MHz		1.7	pA/√Hz	
DC PERFORMANCE					
Open-loop voltage gain (A <sub>OL</sub> )			68	dB	
Input offset voltage	T <sub>A</sub> = +25°C		1	mV	
Average offset voltage drift	T <sub>A</sub> = −40°C to +85°C		2.6	μV/°C	
Input bias current	T <sub>A</sub> = +25°C		6	μA	
Average bias current drift	T <sub>A</sub> = −40°C to +85°C		20	nA/°C	
Input offset current	T <sub>A</sub> = +25°C		1.6	μA	
Average offset current drift	T <sub>A</sub> = −40°C to +85°C		4	nA/°C	
INPUT					
Common-mode input range high			0.4	V	
Common-mode input range low			−0.4		
Common-mode rejection ratio			90	dB	
Differential input impedance			1.3    1.8	MΩ    pF	
Common-mode input impedance			1.0    2.3		

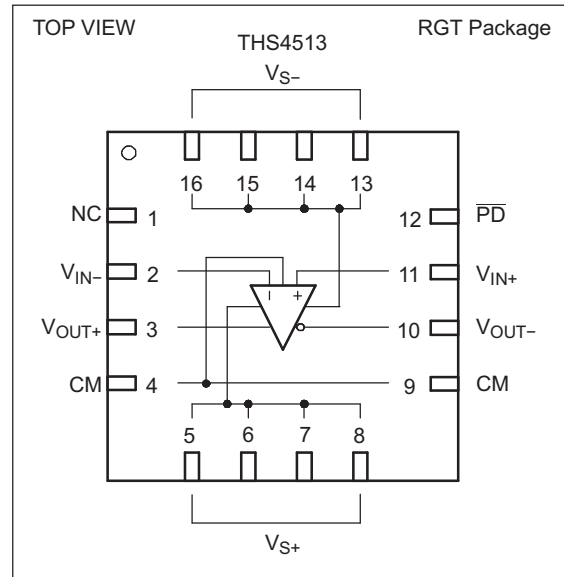
(1) Test levels: (A) 100% tested at  $+25^\circ\text{C}$ . Over-temperature limits by characterization and simulation. (B) Limits set by characterization and simulation. (C) Typical value only for information.

**ELECTRICAL CHARACTERISTICS:  $V_{S+} - V_{S-} = 3\text{ V}$  (continued)**

Test conditions at  $V_{S+} = 1.5\text{ V}$ ,  $V_{S-} = -1.5\text{ V}$ ,  $G = 0\text{ dB}$ ,  $CM = \text{open}$ ,  $V_O = 1\text{ V}_{PP}$ ,  $R_F = 348\text{ }\Omega$ ,  $R_L = 200\text{-}\Omega$  differential,  $T_A = +25^\circ\text{C}$ , single-ended input, differential output, and input and output referenced to midsupply, unless otherwise noted.

PARAMETER	TEST CONDITIONS	TYP	UNIT	TEST LEVEL <sup>(1)</sup>
OUTPUT				C
Maximum output voltage high	Each output with 100 Ω to midsupply	0.45	V	
Minimum output voltage low		−0.45	V	
Differential output voltage swing		1.8	V	
Differential output current drive	R <sub>L</sub> = 10 Ω	50	mA	
Output balance error	V <sub>O</sub> = 100 mV, f = 1 MHz	−54	dB	
Closed-loop output Impedance	f = 1 MHz	0.3	Ω	
OUTPUT COMMON-MODE VOLTAGE CONTROL				
Small-signal bandwidth		150	MHz	
Slew rate		60	V/μs	
Gain		1	V/V	
Output common-mode offset from CM input	−0.5 V < CM < 0.5 V	4	mV	
CM input bias current	−0.5 V < CM < 0.5 V	±40	μA	
CM input voltage range		−1.5 to 1.5	V	
CM input impedance		20    1	kΩ    pF	
CM default voltage		0	V	
POWER SUPPLY				
Quiescent current		34.8	mA	
Power-supply rejection (±PSRR)		80	dB	
POWER-DOWN				
Enable voltage threshold	Referenced to V <sub>S−</sub> , assured on above 2.1 V + V <sub>S−</sub>	> 2.1	V	
Disable voltage threshold	Assured off below 0.7 V + V <sub>S−</sub>	< 0.7	V	
Power-down quiescent current		0.46	mA	
Input bias current	PD = V <sub>S−</sub>	65	μA	
Input impedance		50    2	kΩ    pF	
Turn-on time delay	Measured to output on	100	ns	
Turn-off time delay	Measured to output off	10	μs	

## DEVICE INFORMATION



## TERMINAL FUNCTIONS

TERMINAL (RGT PACKAGE)		DESCRIPTION
NO.	NAME	
1	NC	No internal connection
2	V <sub>IN-</sub>	Inverting amplifier input
3	V <sub>OUT+</sub>	Noninverting amplifier output
4, 9	CM	Common-mode voltage input
5-8	V <sub>S+</sub>	Positive amplifier power-supply input
10	V <sub>OUT-</sub>	Inverted amplifier output
11	V <sub>IN+</sub>	Noninverting amplifier input
12	$\overline{\text{PD}}$	Power-down; $\overline{\text{PD}}$ = logic low puts part into low-power mode, $\overline{\text{PD}}$ = logic high or open for normal operation
13-16	V <sub>S-</sub>	Negative amplifier power-supply input

**TYPICAL CHARACTERISTICS:  $V_{S+} - V_{S-} = 5\text{ V}$** 

Small-Signal Frequency Response	G = 0 dB, $V_{OD} = 100\text{ mV}_{PP}$		<a href="#">Figure 1</a>
	G = 6 dB, $V_{OD} = 100\text{ mV}_{PP}$		<a href="#">Figure 2</a>
Large-Signal Frequency Response	G = 0 dB, $V_{OD} = 2\text{ V}_{PP}$		<a href="#">Figure 3</a>
	G = 6 dB, $V_{OD} = 2\text{ V}_{PP}$		<a href="#">Figure 4</a>
Harmonic Distortion	HD <sub>2</sub> , G = 0 dB, $V_{OD} = 2\text{ V}_{PP}$	vs Frequency	<a href="#">Figure 5</a>
	HD <sub>3</sub> , G = 0 dB, $V_{OD} = 2\text{ V}_{PP}$	vs Frequency	<a href="#">Figure 6</a>
	HD <sub>2</sub> , G = 6 dB, $V_{OD} = 2\text{ V}_{PP}$	vs Frequency	<a href="#">Figure 7</a>
	HD <sub>3</sub> , G = 6 dB, $V_{OD} = 2\text{ V}_{PP}$	vs Frequency	<a href="#">Figure 8</a>
	HD <sub>2</sub> , G = 0 dB	vs Output Voltage	<a href="#">Figure 9</a>
	HD <sub>3</sub> , G = 0 dB	vs Output Voltage	<a href="#">Figure 10</a>
	HD <sub>2</sub> , G = 0 dB	vs CM Output Voltage	<a href="#">Figure 11</a>
	HD <sub>3</sub> , G = 0 dB	vs CM Output Voltage	<a href="#">Figure 12</a>
Intermodulation Distortion	IMD <sub>2</sub> , G = 0 dB	vs Frequency	<a href="#">Figure 13</a>
	IMD <sub>3</sub> , G = 0 dB	vs Frequency	<a href="#">Figure 14</a>
Output Intercept Point	OIP <sub>2</sub>	vs Frequency	<a href="#">Figure 15</a>
	OIP <sub>3</sub>	vs Frequency	<a href="#">Figure 16</a>
S-Parameters		vs Frequency	<a href="#">Figure 17</a>
Transition Rate		vs Output Voltage	<a href="#">Figure 18</a>
Transient Response			<a href="#">Figure 19</a>
Settling Time			<a href="#">Figure 20</a>
Rejection Ratio		vs Frequency	<a href="#">Figure 21</a>
Output Impedance		vs Frequency	<a href="#">Figure 22</a>
Overdrive Recovery			<a href="#">Figure 23</a>
Output Voltage Swing		vs Load Resistance	<a href="#">Figure 24</a>
Turn-Off Time			<a href="#">Figure 25</a>
Turn-On Time			<a href="#">Figure 26</a>
Input Offset Voltage		vs Input Common-Mode Voltage	<a href="#">Figure 27</a>
Open-Loop Gain		vs Frequency	<a href="#">Figure 28</a>
Input-Referred Noise		vs Frequency	<a href="#">Figure 29</a>
Noise Figure		vs Frequency	<a href="#">Figure 30</a>
Quiescent Current		vs Supply Voltage	<a href="#">Figure 31</a>
Power-Supply Current		vs Supply Voltage in Power-Down Mode	<a href="#">Figure 32</a>
Output Balance Error		vs Frequency	<a href="#">Figure 33</a>
CM Input Impedance		vs Frequency	<a href="#">Figure 34</a>
CM Small-Signal Frequency Response			<a href="#">Figure 35</a>
CM Input Bias Current		vs CM Input Voltage	<a href="#">Figure 36</a>
Differential Output Offset Voltage		vs CM Input Voltage	<a href="#">Figure 37</a>
Output Common-Mode Offset		vs CM Input Voltage	<a href="#">Figure 38</a>



## TYPICAL CHARACTERISTICS: $V_{S+} - V_{S-} = 5\text{ V}$

Test conditions at  $V_{S+} = +2.5\text{ V}$ ,  $V_{S-} = -2.5\text{ V}$ , CM = open,  $V_O = 2\text{ V}_{pp}$ ,  $R_F = 348\ \Omega$ ,  $R_L = 200\text{-}\Omega$  differential,  $G = 0\text{ dB}$ , single-ended input, and input and output referenced to midsupply, unless otherwise noted.

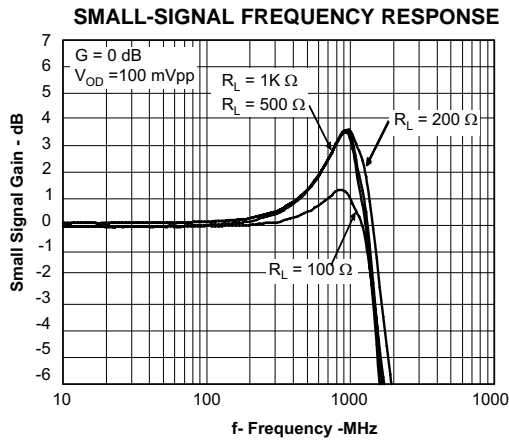


Figure 1.

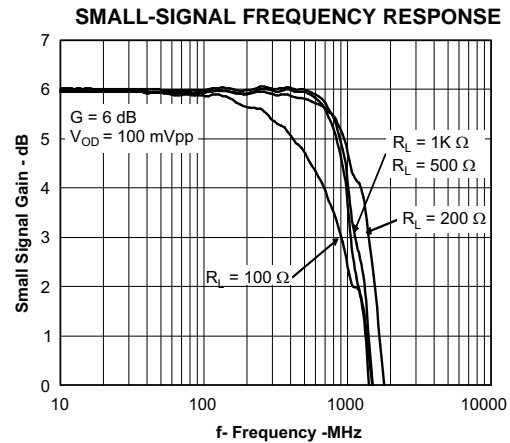


Figure 2.

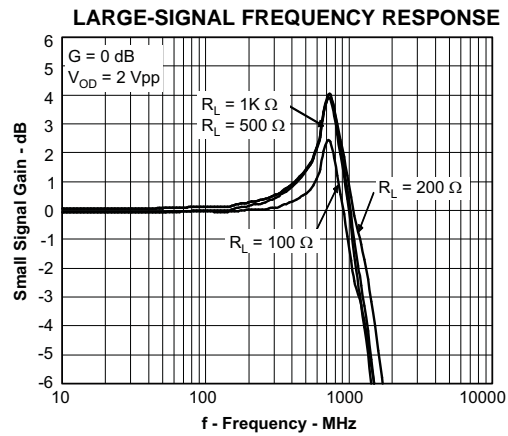


Figure 3.

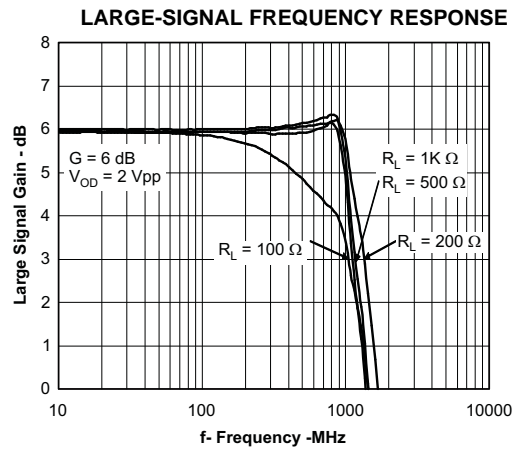


Figure 4.

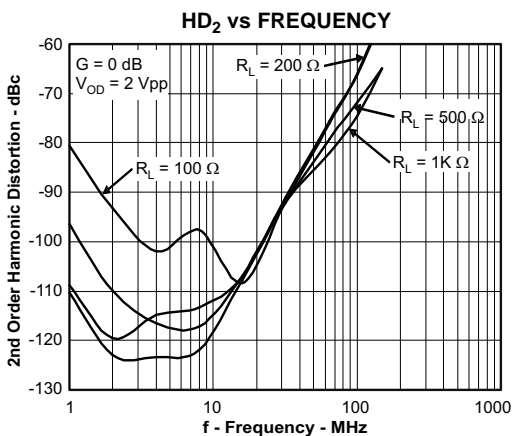


Figure 5.

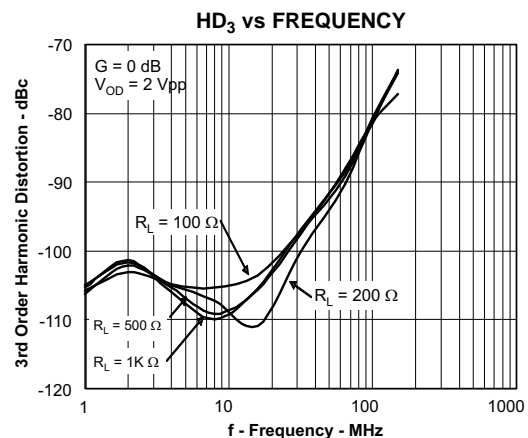


Figure 6.

### TYPICAL CHARACTERISTICS: $V_{S+} - V_{S-} = 5\text{ V}$ (continued)

Test conditions at  $V_{S+} = +2.5\text{ V}$ ,  $V_{S-} = -2.5\text{ V}$ , CM = open,  $V_O = 2\text{ V}_{PP}$ ,  $R_F = 348\ \Omega$ ,  $R_L = 200\text{-}\Omega$  differential,  $G = 0\text{ dB}$ , single-ended input, and input and output referenced to midsupply, unless otherwise noted.

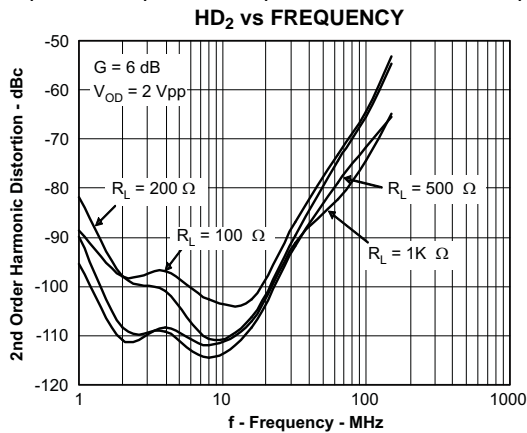


Figure 7.

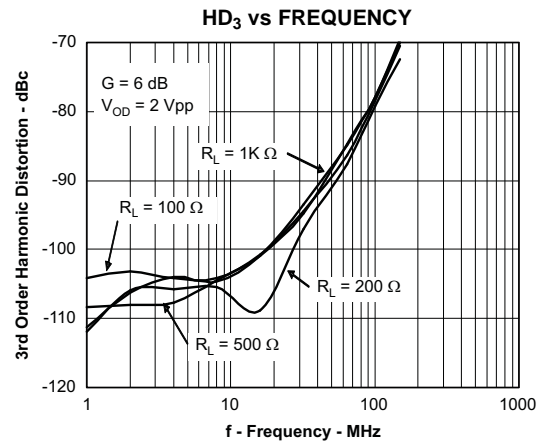


Figure 8.

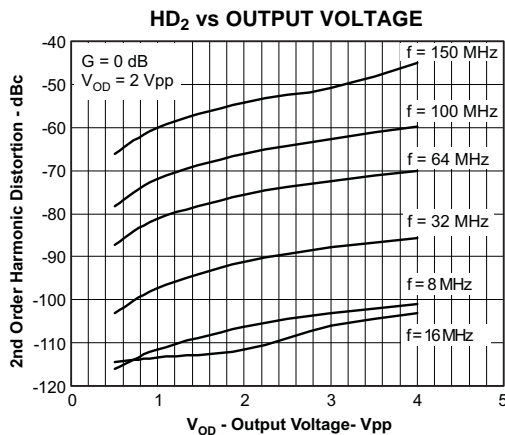


Figure 9.

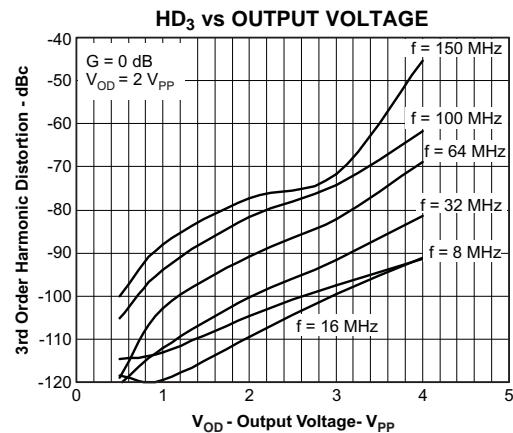


Figure 10.

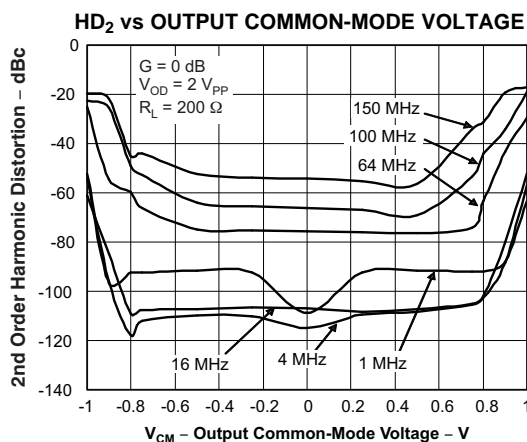


Figure 11.

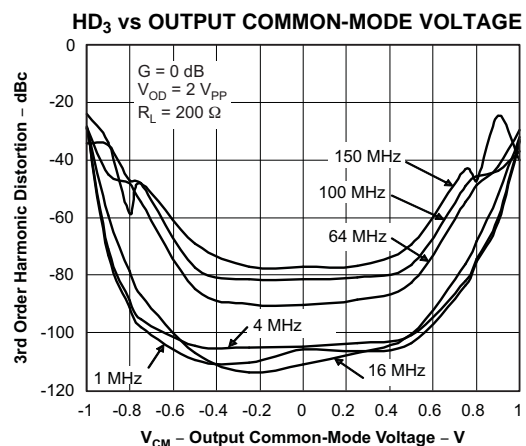
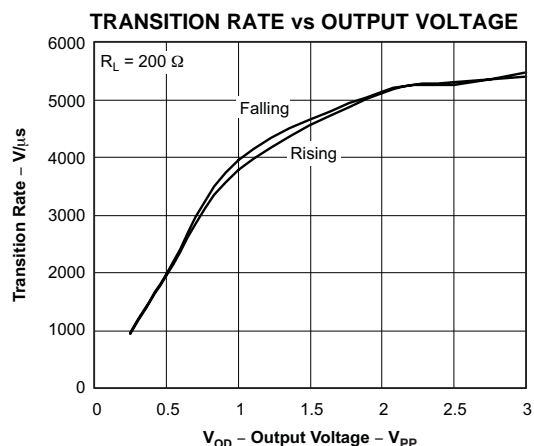
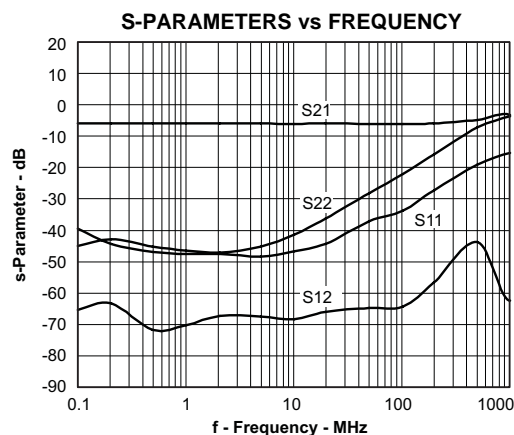
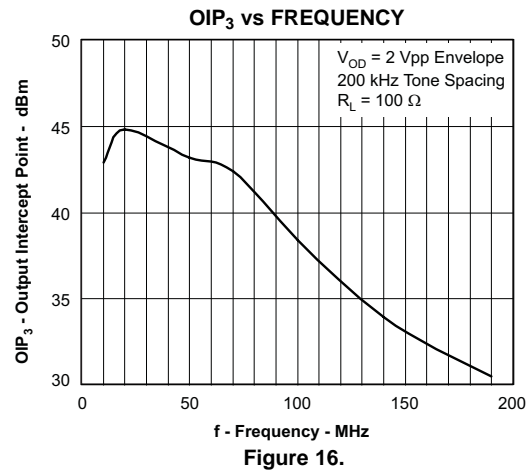
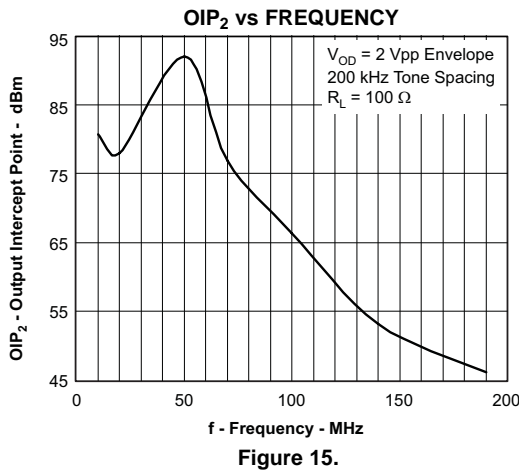
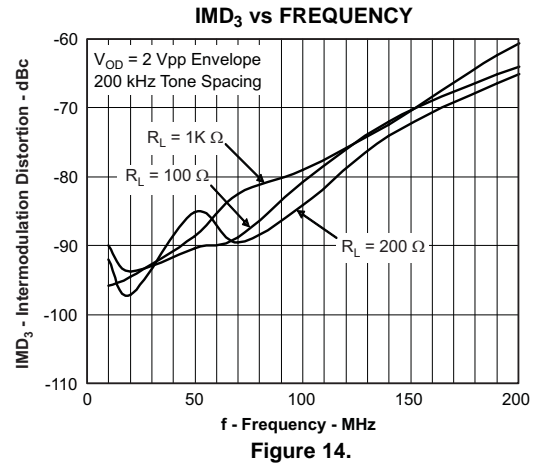
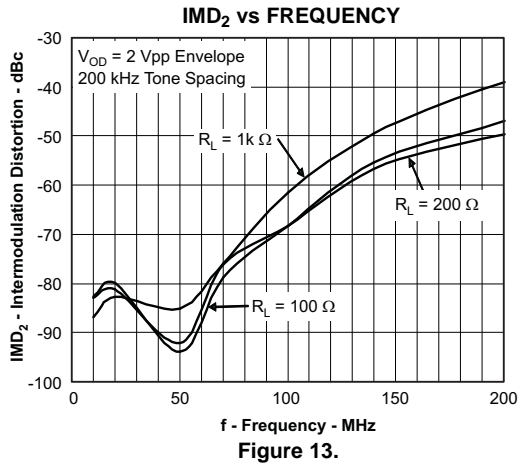


Figure 12.

## TYPICAL CHARACTERISTICS: $V_{S+} - V_{S-} = 5\text{ V}$ (continued)

Test conditions at  $V_{S+} = +2.5\text{ V}$ ,  $V_{S-} = -2.5\text{ V}$ , CM = open,  $V_O = 2\text{ V}_{PP}$ ,  $R_F = 348\ \Omega$ ,  $R_L = 200\text{-}\Omega$  differential, G = 0 dB, single-ended input, and input and output referenced to midsupply, unless otherwise noted.



## TYPICAL CHARACTERISTICS: $V_{S+} - V_{S-} = 5\text{ V}$ (continued)

Test conditions at  $V_{S+} = +2.5\text{ V}$ ,  $V_{S-} = -2.5\text{ V}$ , CM = open,  $V_O = 2\text{ V}_{PP}$ ,  $R_F = 348\ \Omega$ ,  $R_L = 200\text{-}\Omega$  differential,  $G = 0\text{ dB}$ , single-ended input, and input and output referenced to midsupply, unless otherwise noted.

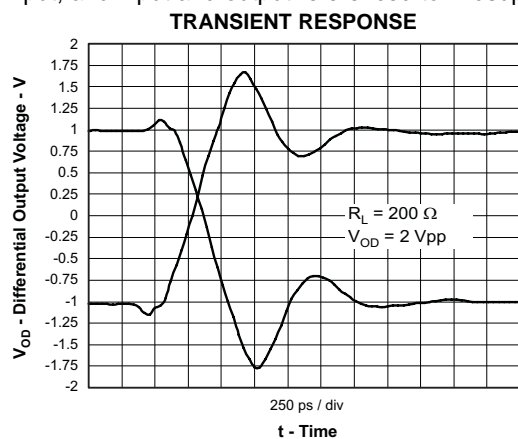


Figure 19.

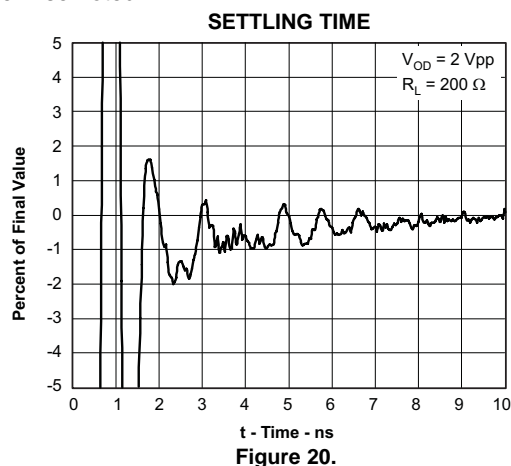


Figure 20.

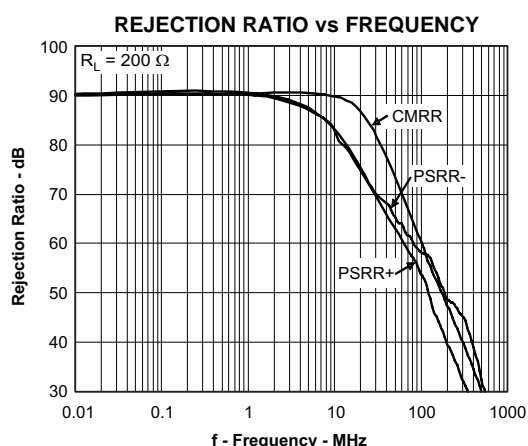


Figure 21.

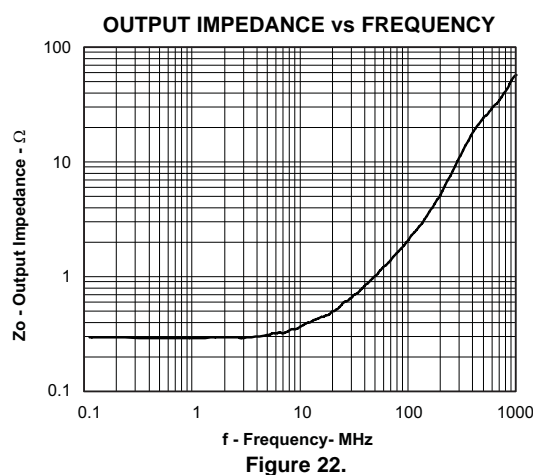


Figure 22.

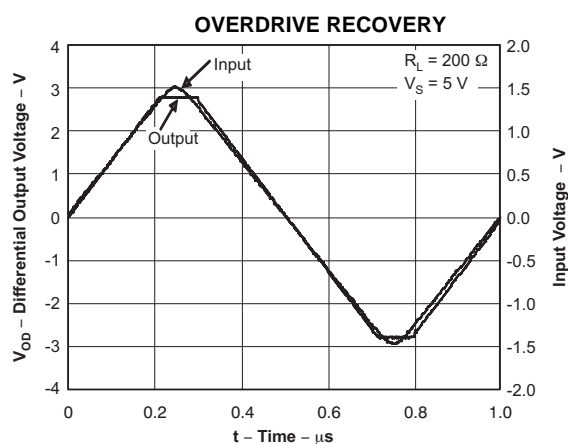


Figure 23.

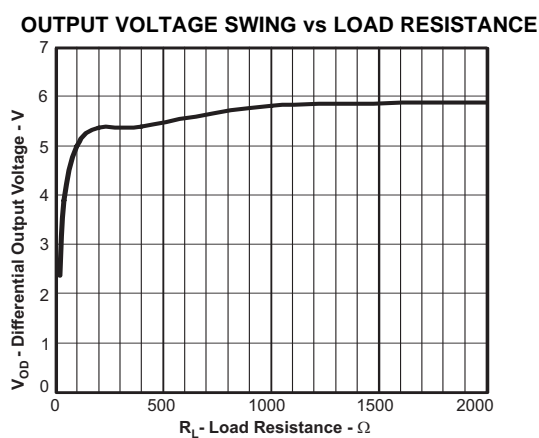
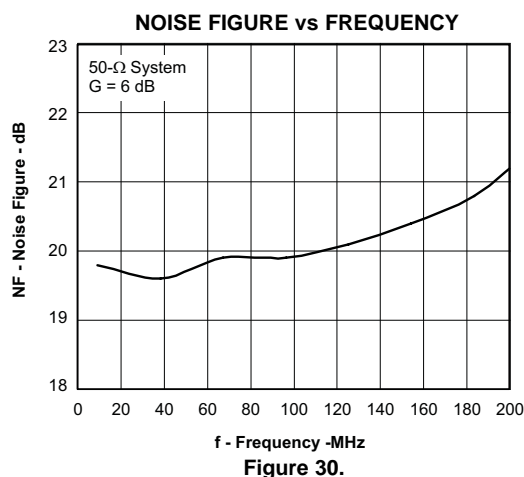
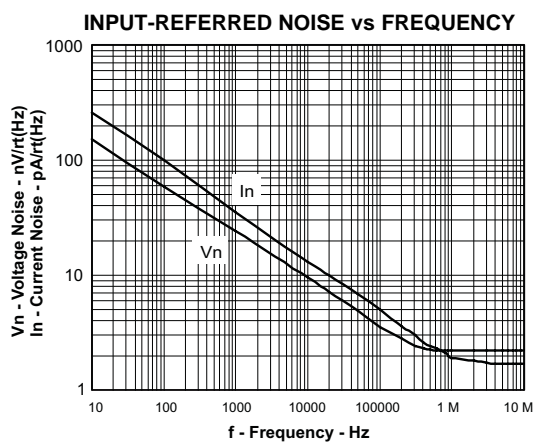
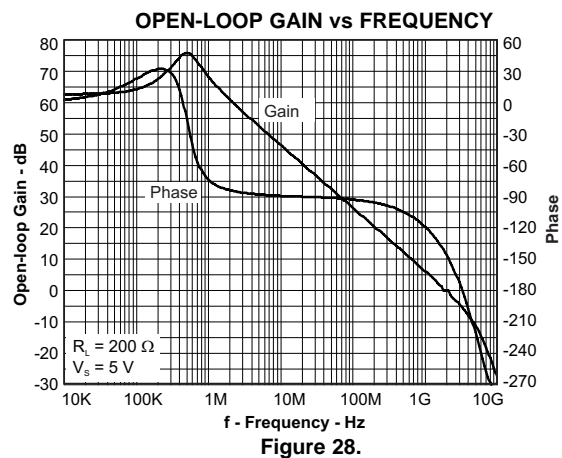
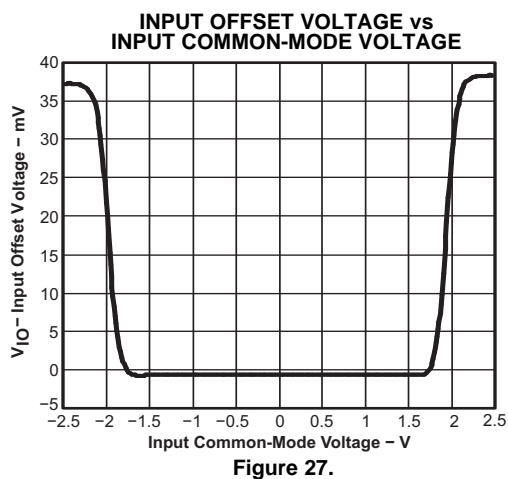
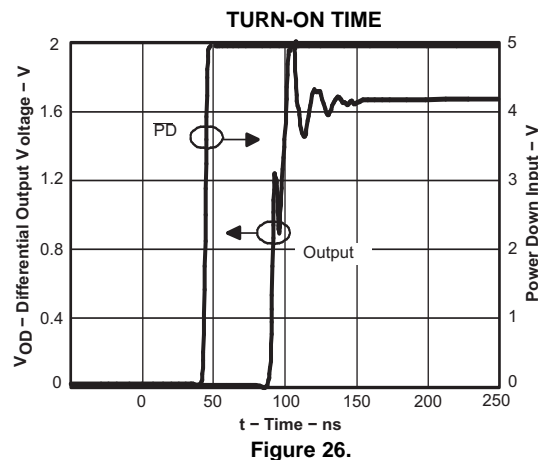
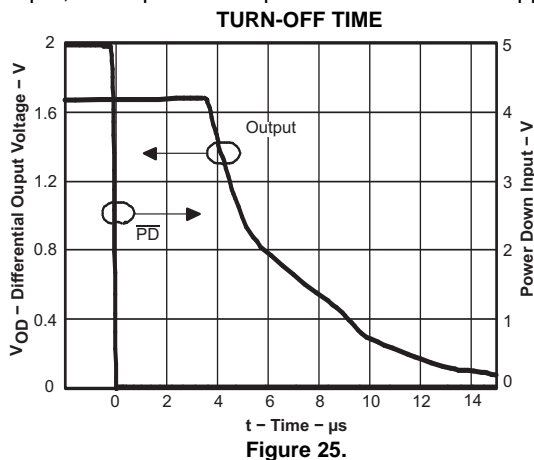


Figure 24.

## TYPICAL CHARACTERISTICS: $V_{S+} - V_{S-} = 5\text{ V}$ (continued)

Test conditions at  $V_{S+} = +2.5\text{ V}$ ,  $V_{S-} = -2.5\text{ V}$ , CM = open,  $V_O = 2\text{ V}_{PP}$ ,  $R_F = 348\ \Omega$ ,  $R_L = 200\text{-}\Omega$  differential,  $G = 0\text{ dB}$ , single-ended input, and input and output referenced to midsupply, unless otherwise noted.



### TYPICAL CHARACTERISTICS: $V_{S+} - V_{S-} = 5\text{ V}$ (continued)

Test conditions at  $V_{S+} = +2.5\text{ V}$ ,  $V_{S-} = -2.5\text{ V}$ , CM = open,  $V_O = 2\text{ V}_{PP}$ ,  $R_F = 348\ \Omega$ ,  $R_L = 200\text{-}\Omega$  differential,  $G = 0\text{ dB}$ , single-ended input, and input and output referenced to midsupply, unless otherwise noted.

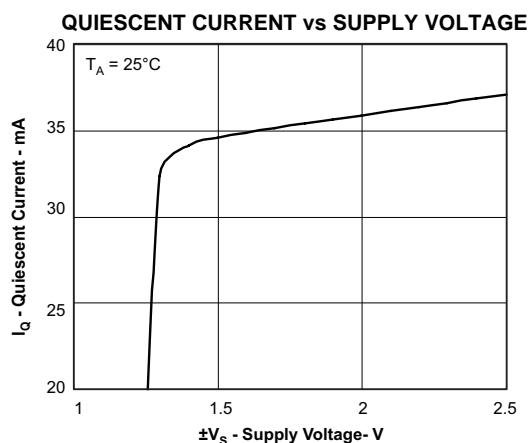


Figure 31.

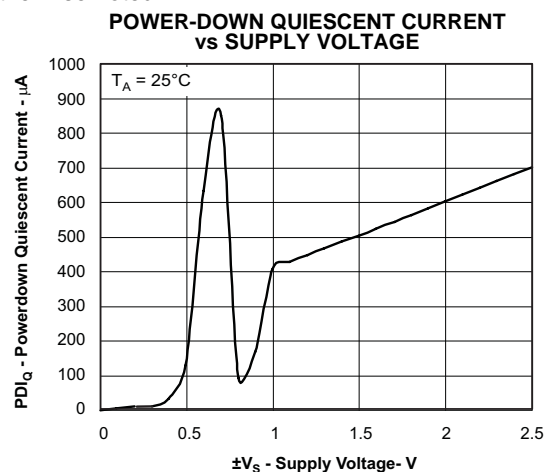


Figure 32.

### OUTPUT BALANCE ERROR RESPONSE vs FREQUENCY

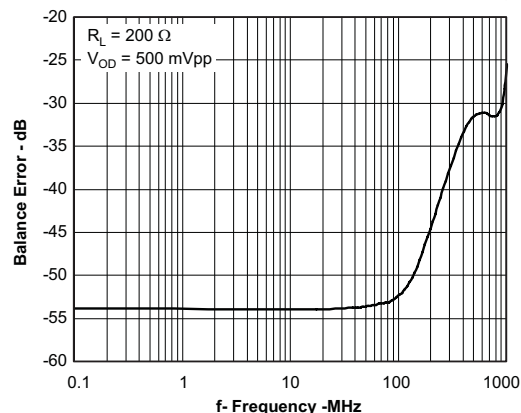


Figure 33.

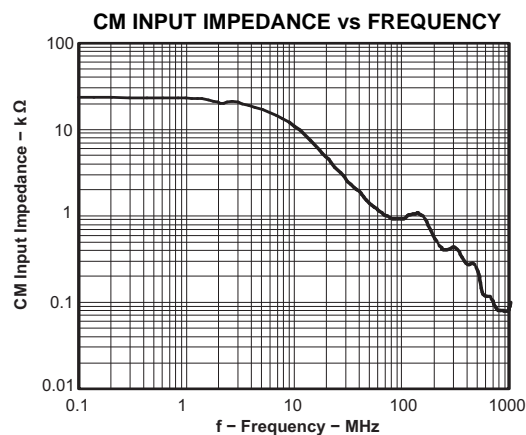


Figure 34.

### CM SMALL-SIGNAL FREQUENCY RESPONSE

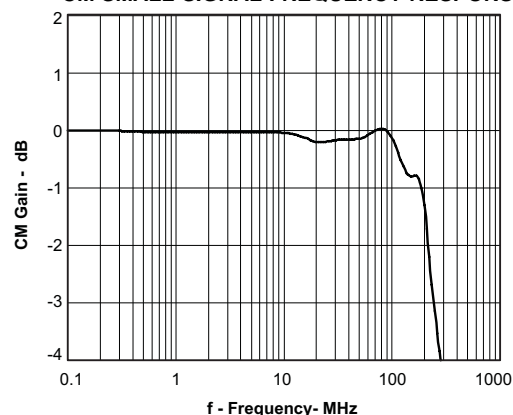


Figure 35.

### CM INPUT BIAS CURRENT vs CM INPUT VOLTAGE

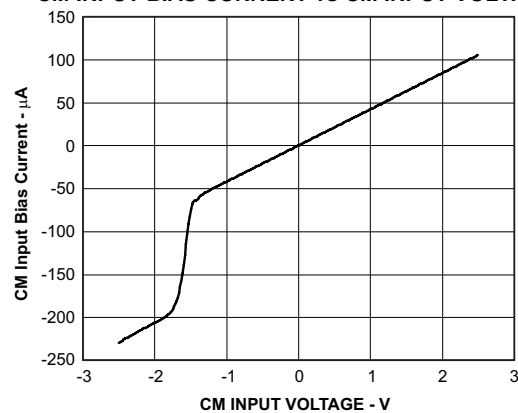


Figure 36.

### TYPICAL CHARACTERISTICS: $V_{S+} - V_{S-} = 5\text{ V}$ (continued)

Test conditions at  $V_{S+} = +2.5\text{ V}$ ,  $V_{S-} = -2.5\text{ V}$ , CM = open,  $V_O = 2\text{ V}_{PP}$ ,  $R_F = 348\ \Omega$ ,  $R_L = 200\text{-}\Omega$  differential,  $G = 0\text{ dB}$ , single-ended input, and input and output referenced to midsupply, unless otherwise noted.

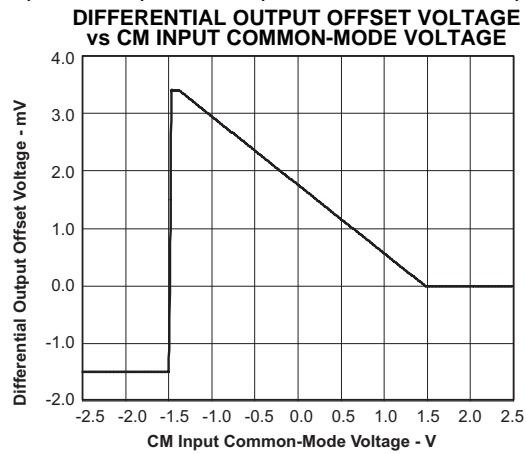


Figure 37.

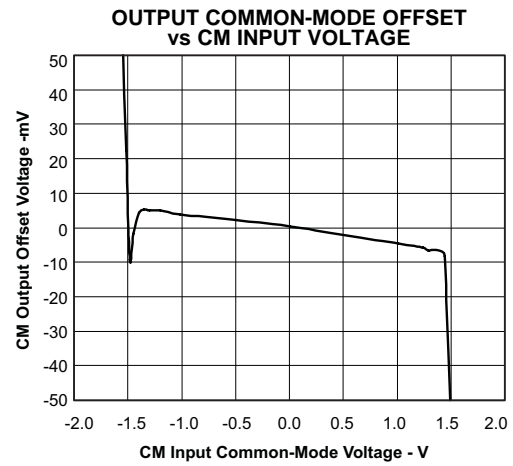


Figure 38.

**TYPICAL CHARACTERISTICS:  $V_{S+} - V_{S-} = 3\text{ V}$** 

Small-Signal Frequency Response	G = 0 dB, $V_{OD} = 100\text{ mV}_{PP}$		<a href="#">Figure 39</a>
	G = 6 dB, $V_{OD} = 100\text{ mV}_{PP}$		<a href="#">Figure 40</a>
Large-Signal Frequency Response	G = 0 dB, $V_{OD} = 1\text{ V}_{PP}$		<a href="#">Figure 41</a>
	G = 6 dB, $V_{OD} = 1\text{ V}_{PP}$		<a href="#">Figure 42</a>
Harmonic Distortion	HD <sub>2</sub> , G = 0 dB, $V_{OD} = 1\text{ V}_{PP}$	vs Frequency	<a href="#">Figure 43</a>
	HD <sub>3</sub> , G = 0 dB, $V_{OD} = 1\text{ V}_{PP}$	vs Frequency	<a href="#">Figure 44</a>
	HD <sub>2</sub> , G = 6 dB, $V_{OD} = 1\text{ V}_{PP}$	vs Frequency	<a href="#">Figure 45</a>
	HD <sub>3</sub> , G = 6 dB, $V_{OD} = 1\text{ V}_{PP}$	vs Frequency	<a href="#">Figure 46</a>
	HD <sub>2</sub> , G = 0 dB	vs Output Voltage	<a href="#">Figure 47</a>
	HD <sub>3</sub> , G = 0 dB	vs Output Voltage	<a href="#">Figure 48</a>
	HD <sub>2</sub> , G = 0 dB	vs CM Output Voltage	<a href="#">Figure 49</a>
	HD <sub>3</sub> , G = 0 dB	vs CM Output Voltage	<a href="#">Figure 50</a>
Intermodulation Distortion	IMD <sub>2</sub> , G = 0 dB	vs Frequency	<a href="#">Figure 51</a>
	IMD <sub>3</sub> , G = 0 dB	vs Frequency	<a href="#">Figure 52</a>
Output Intercept Point	OIP <sub>2</sub>	vs Frequency	<a href="#">Figure 53</a>
	OIP <sub>3</sub>	vs Frequency	<a href="#">Figure 54</a>
S-Parameters		vs Frequency	<a href="#">Figure 55</a>
Transition Rate		vs Output Voltage	<a href="#">Figure 56</a>
Transient Response			<a href="#">Figure 57</a>
Settling Time			<a href="#">Figure 58</a>
Output Voltage Swing		vs Load Resistance	<a href="#">Figure 59</a>
Rejection Ratio		vs Frequency	<a href="#">Figure 60</a>
Overdrive Recovery			<a href="#">Figure 61</a>
Output Impedance		vs Frequency	<a href="#">Figure 62</a>
Turn-Off Time			<a href="#">Figure 63</a>
Turn-On Time			<a href="#">Figure 64</a>
Output Balance Error		vs Frequency	<a href="#">Figure 65</a>
Noise Figure		vs Frequency	<a href="#">Figure 66</a>
CM Small-Signal Frequency Response			<a href="#">Figure 67</a>
CM Input Impedance		vs Frequency	<a href="#">Figure 68</a>
Differential Output Offset Voltage		vs CM Input Voltage	<a href="#">Figure 69</a>
Output Common-Mode Offset		vs CM Input Voltage	<a href="#">Figure 70</a>



## TYPICAL CHARACTERISTICS: $V_{S+} - V_{S-} = 3\text{ V}$

Test conditions at  $V_{S+} = +1.5\text{ V}$ ,  $V_{S-} = -1.5\text{ V}$ , CM = open,  $V_{OD} = 1\text{ V}_{PP}$ ,  $R_F = 348\ \Omega$ ,  $R_L = 200\text{-}\Omega$  differential, G = 0 dB, single-ended input, and input and output referenced to midsupply, unless otherwise noted.

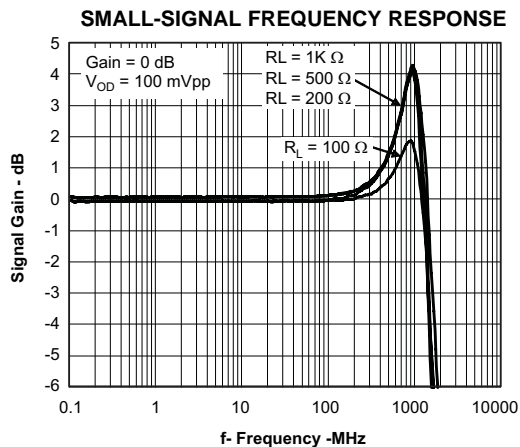


Figure 39.

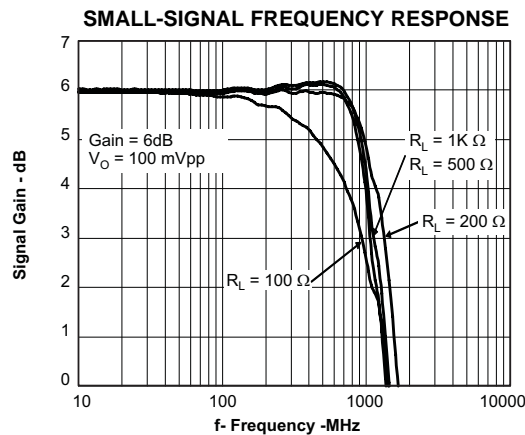


Figure 40.

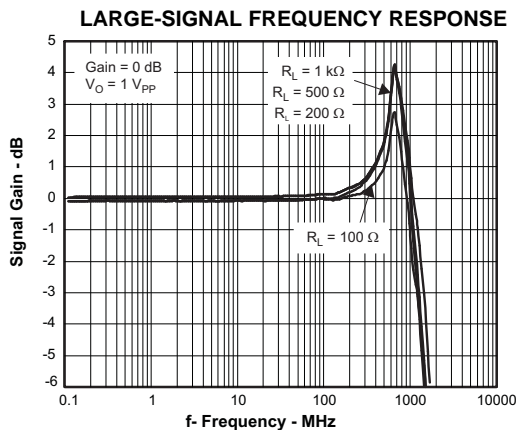


Figure 41.

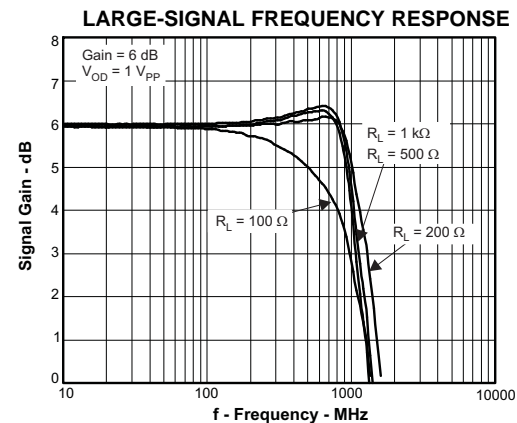


Figure 42.

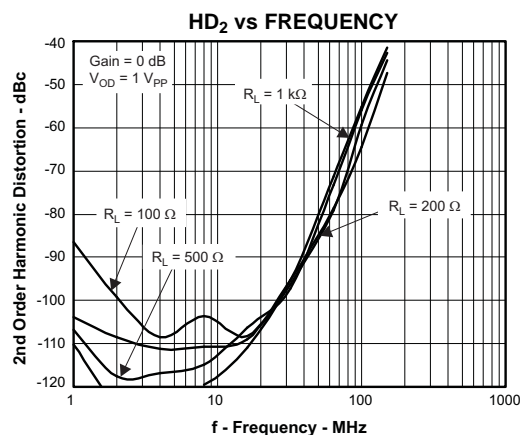


Figure 43.

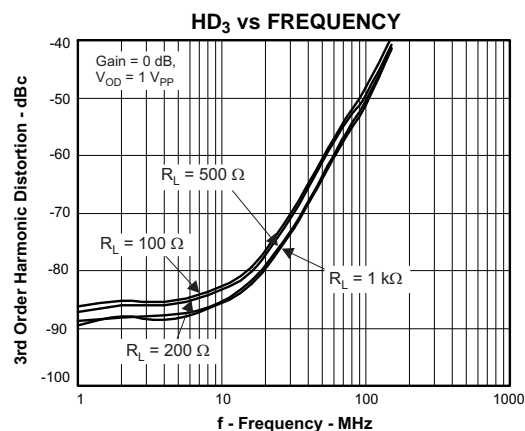


Figure 44.

### TYPICAL CHARACTERISTICS: $V_{S+} - V_{S-} = 3\text{ V}$ (continued)

Test conditions at  $V_{S+} = +1.5\text{ V}$ ,  $V_{S-} = -1.5\text{ V}$ , CM = open,  $V_{OD} = 1\text{ V}_{PP}$ ,  $R_F = 348\ \Omega$ ,  $R_L = 200\text{-}\Omega$  differential,  $G = 0\text{ dB}$ , single-ended input, and input and output referenced to midsupply, unless otherwise noted.

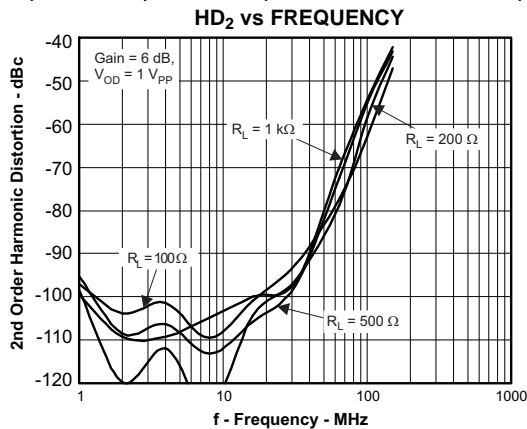


Figure 45.

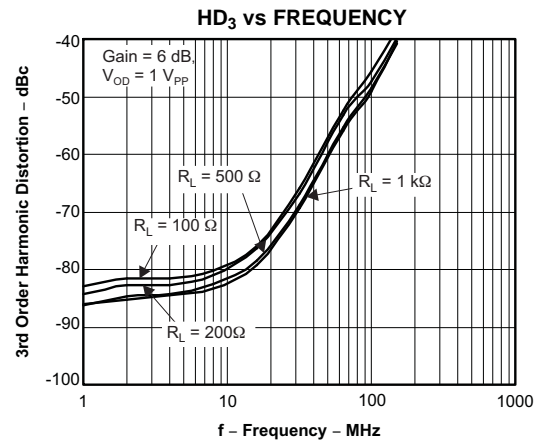


Figure 46.

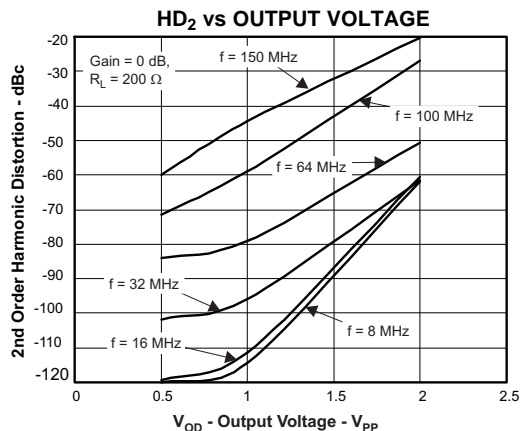


Figure 47.

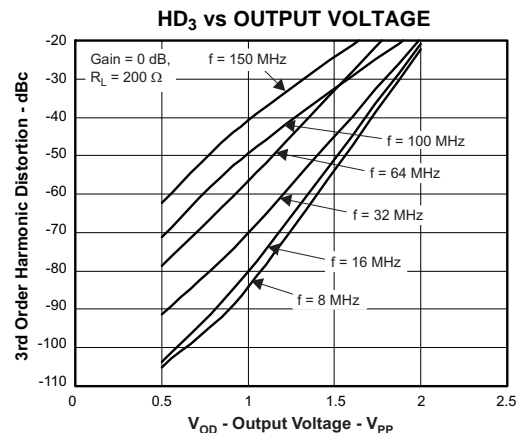


Figure 48.

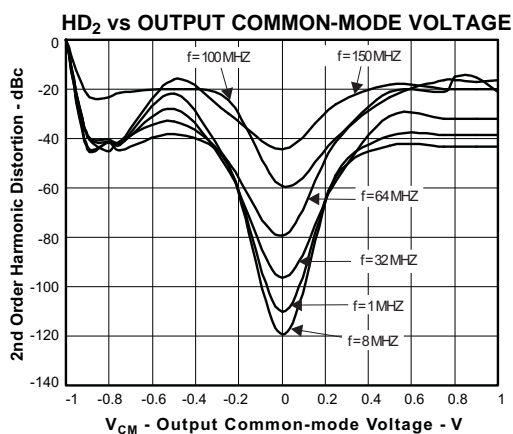


Figure 49.

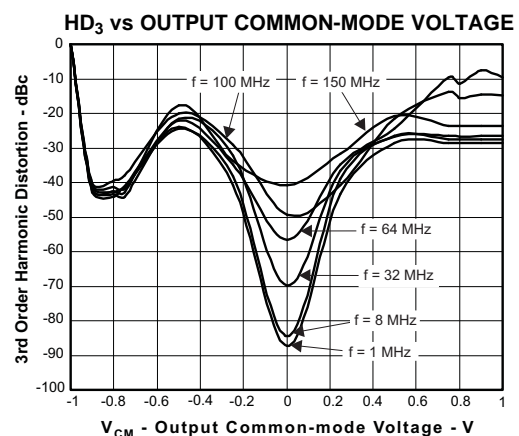


Figure 50.

## TYPICAL CHARACTERISTICS: $V_{S+} - V_{S-} = 3\text{ V}$ (continued)

Test conditions at  $V_{S+} = +1.5\text{ V}$ ,  $V_{S-} = -1.5\text{ V}$ , CM = open,  $V_{OD} = 1\text{ V}_{PP}$ ,  $R_F = 348\ \Omega$ ,  $R_L = 200\text{-}\Omega$  differential, G = 0 dB, single-ended input, and input and output referenced to midsupply, unless otherwise noted.

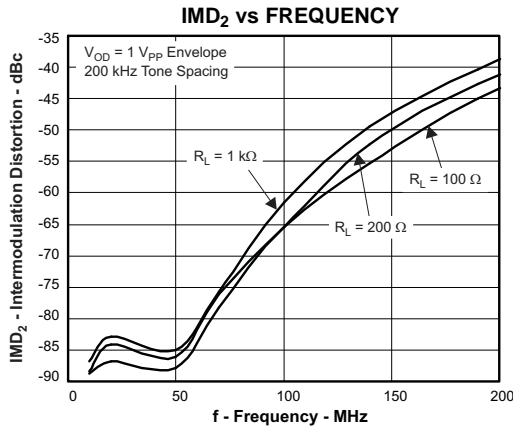


Figure 51.

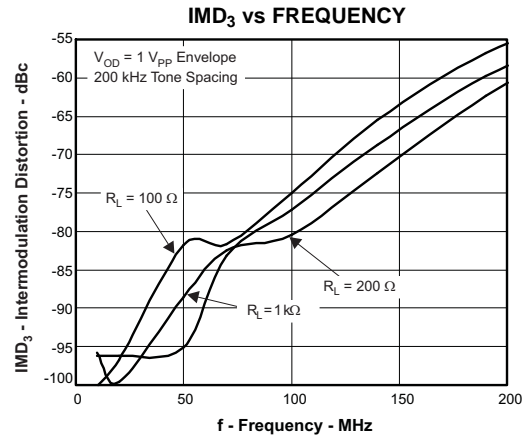


Figure 52.

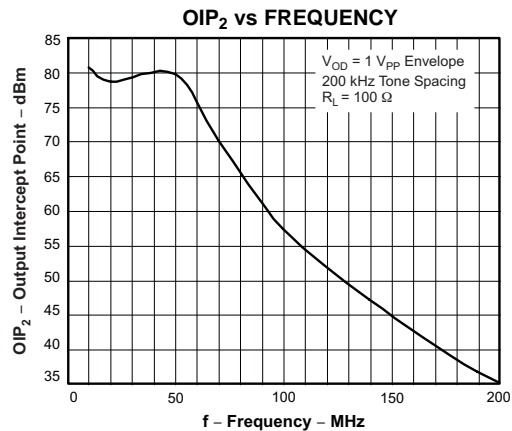


Figure 53.

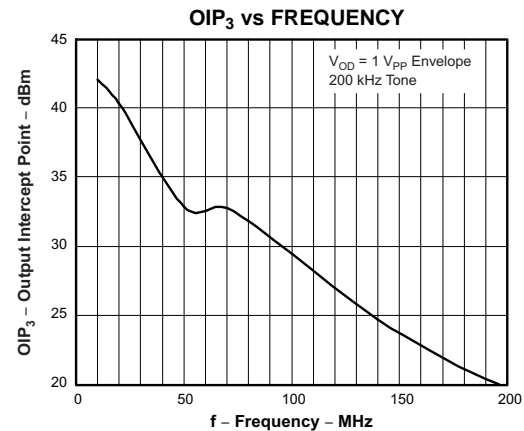


Figure 54.

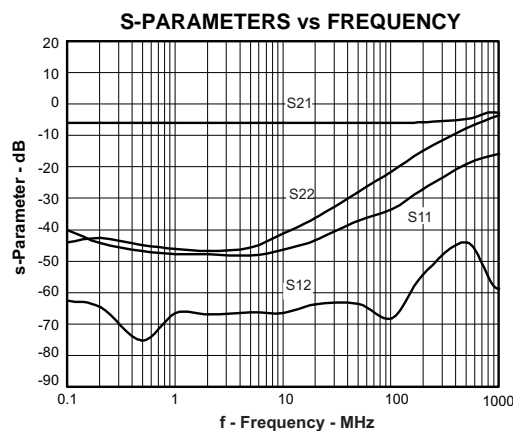


Figure 55.

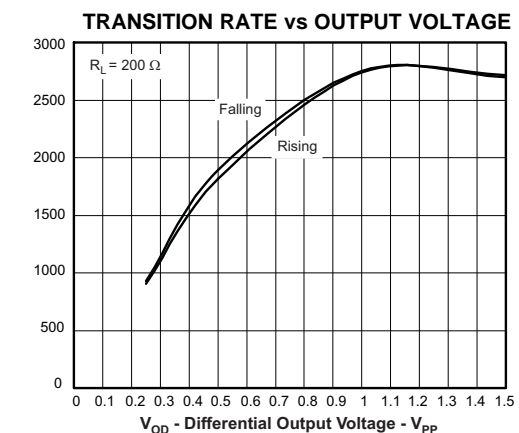


Figure 56.

### TYPICAL CHARACTERISTICS: $V_{S+} - V_{S-} = 3\text{ V}$ (continued)

Test conditions at  $V_{S+} = +1.5\text{ V}$ ,  $V_{S-} = -1.5\text{ V}$ , CM = open,  $V_{OD} = 1\text{ V}_{PP}$ ,  $R_F = 348\ \Omega$ ,  $R_L = 200\text{-}\Omega$  differential,  $G = 0\text{ dB}$ , single-ended input, and input and output referenced to midsupply, unless otherwise noted.

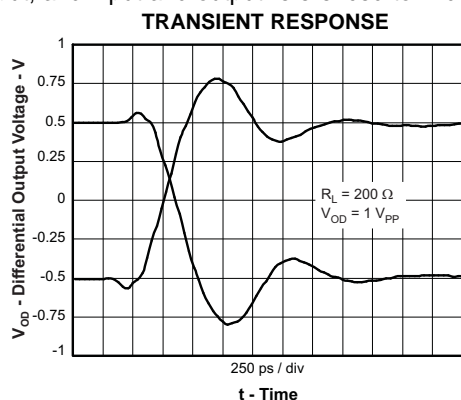


Figure 57.

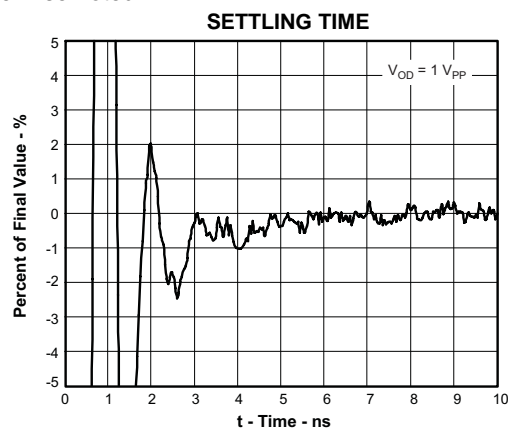


Figure 58.

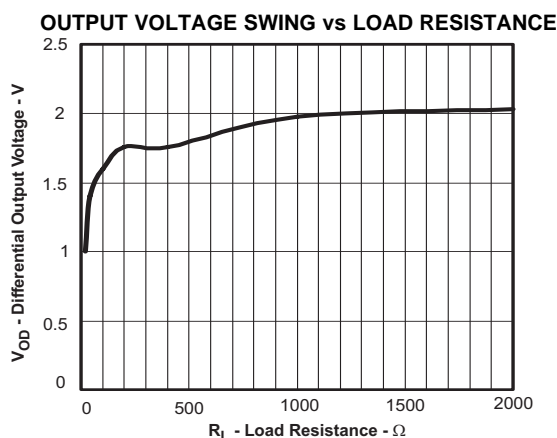


Figure 59.

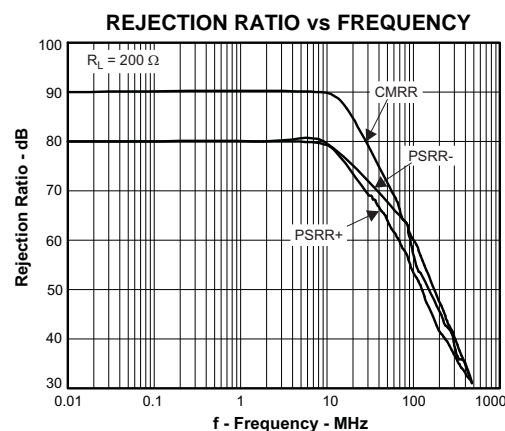


Figure 60.

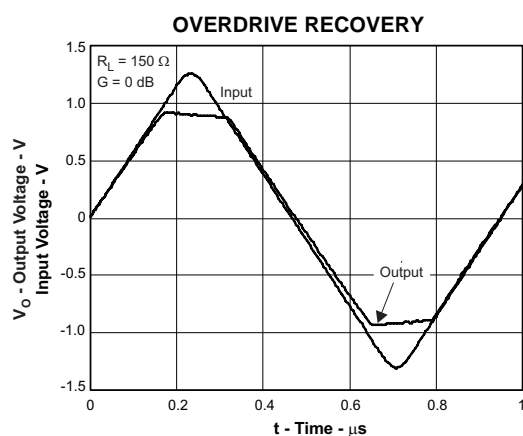


Figure 61.

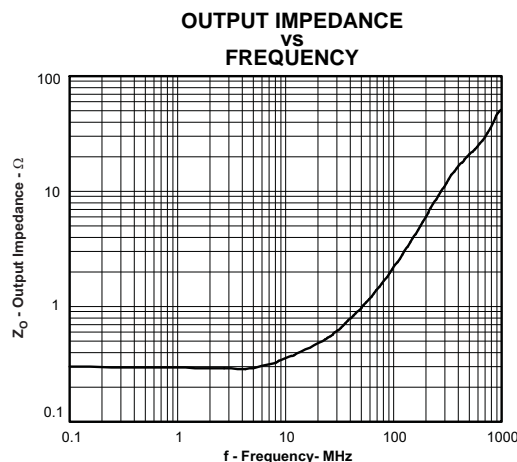


Figure 62.

## TYPICAL CHARACTERISTICS: $V_{S+} - V_{S-} = 3\text{ V}$ (continued)

Test conditions at  $V_{S+} = +1.5\text{ V}$ ,  $V_{S-} = -1.5\text{ V}$ , CM = open,  $V_{OD} = 1\text{ V}_{PP}$ ,  $R_F = 348\ \Omega$ ,  $R_L = 200\text{-}\Omega$  differential,  $G = 0\text{ dB}$ , single-ended input, and input and output referenced to midsupply, unless otherwise noted.

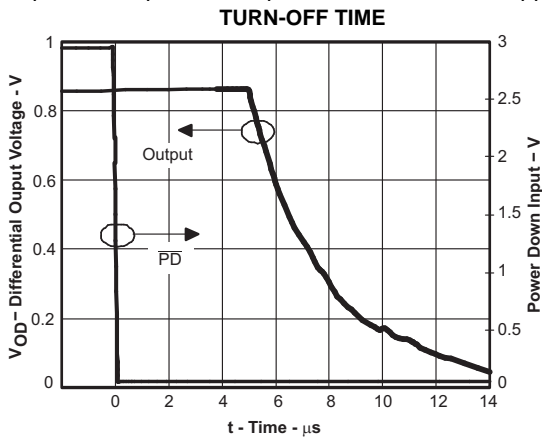


Figure 63.

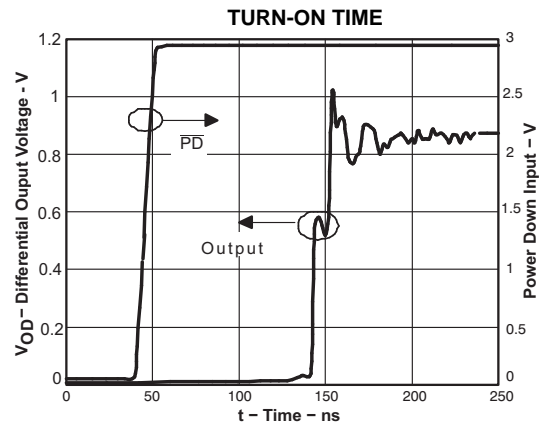


Figure 64.

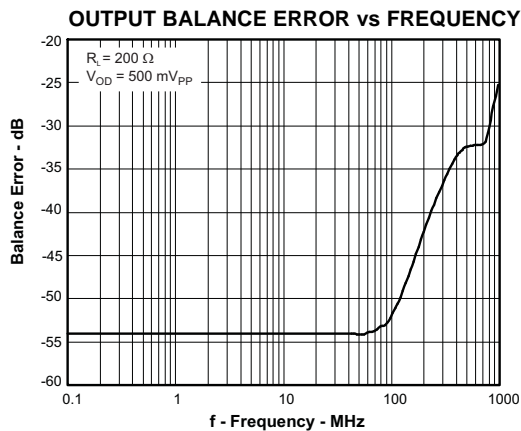


Figure 65.

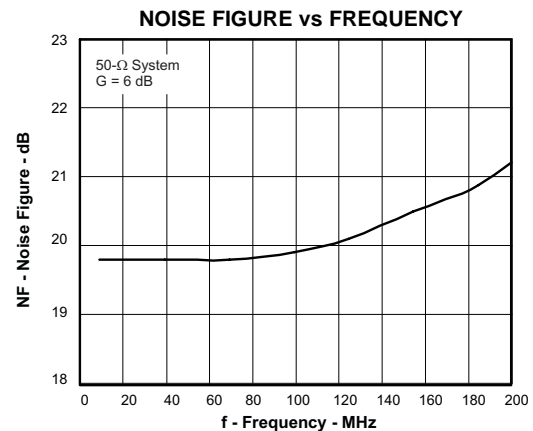


Figure 66.

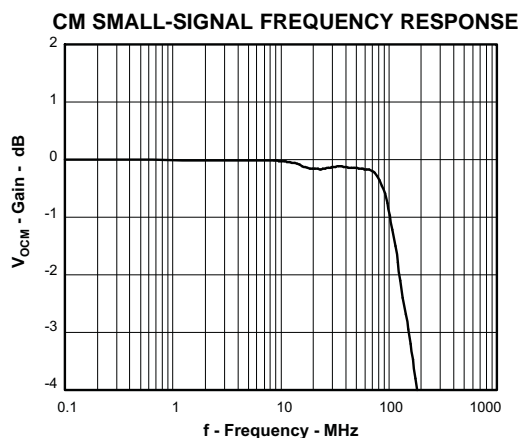


Figure 67.

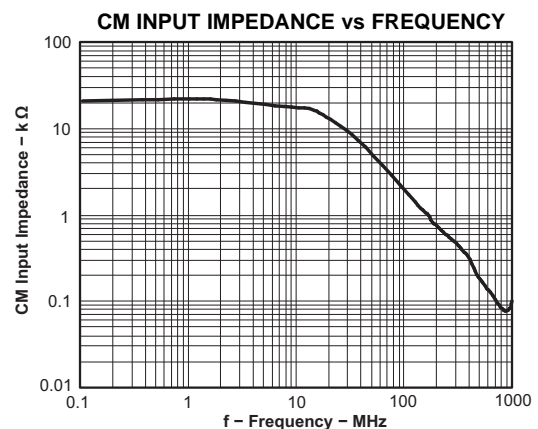


Figure 68.

### TYPICAL CHARACTERISTICS: $V_{S+} - V_{S-} = 3\text{ V}$ (continued)

Test conditions at  $V_{S+} = +1.5\text{ V}$ ,  $V_{S-} = -1.5\text{ V}$ , CM = open,  $V_{OD} = 1\text{ V}_{PP}$ ,  $R_F = 348\ \Omega$ ,  $R_L = 200\text{-}\Omega$  differential,  $G = 0\text{ dB}$ , single-ended input, and input and output referenced to midsupply, unless otherwise noted.

**DIFFERENTIAL OUTPUT OFFSET VOLTAGE vs  
CM INPUT VOLTAGE**

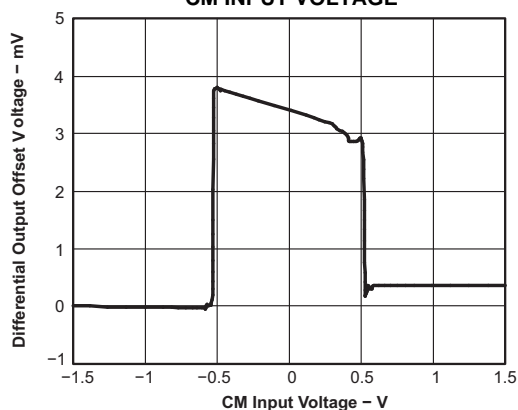


Figure 69.

**OUTPUT COMMON-MODE OFFSET vs CM INPUT VOLTAGE**

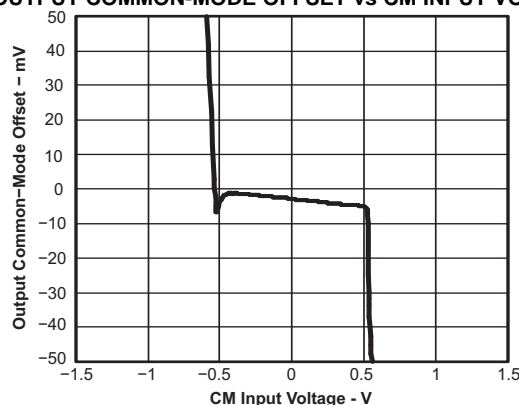


Figure 70.

## TEST CIRCUITS

The THS4513 is tested with the following test circuits built on the evaluation module (EVM). For simplicity, power-supply decoupling is not shown—see [Layout Recommendations](#) in the [Applications](#) section for recommendations. Depending on the test conditions, component values are changed per the following tables, or as otherwise noted. The signal generators used are ac-coupled, 50-Ω sources and a 0.22-μF capacitor and 49.9-Ω resistor to ground are inserted across  $R_{IT}$  on the alternate input to balance the circuit. A split power supply is used to ease the interface to common test equipment, but the amplifier can be operated single-supply as described in the applications section with no impact on performance.

**Table 1. Gain Component Values**

GAIN	$R_F$	$R_G$	$R_{IT}$
0 dB	348 Ω	340 Ω	56.2 Ω
6 dB	348 Ω	165 Ω	61.9 Ω

**Note the gain setting includes 50-Ω source impedance. Components are chosen to achieve gain and 50-Ω input termination.**

**Table 2. Load Component Values**

$R_L$	$R_O$	$R_{OT}$	Atten.
100 Ω	25 Ω	Open	6 dB
200 Ω	86.6 Ω	69.8 Ω	16.8 dB
499 Ω	237 Ω	56.2 Ω	25.5 dB
1k Ω	487 Ω	52.3 Ω	31.8 dB

**Note the total load includes 50-Ω termination by the test equipment. Components are chosen to achieve load and 50-Ω line termination through a 1:1 transformer.**

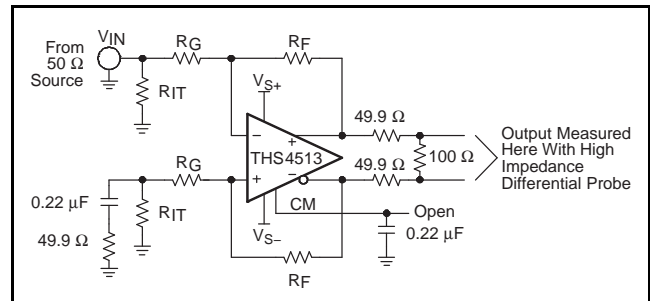
Due to the voltage divider on the output formed by the load component values, the amplifier output is attenuated. The column *Atten* in [Table 2](#) shows the attenuation expected from the resistor divider. When using a transformer at the output as shown in [Figure 72](#), the signal will see slightly more loss, and these numbers will be approximate.

### Frequency Response

The circuit shown in [Figure 71](#) is used to measure the frequency response of the circuit.

A network analyzer is used as the signal source and as the measurement device. The output impedance of the network analyzer is 50 Ω.  $R_{IT}$  and  $R_G$  are chosen to impedance match to 50 Ω, and to maintain the proper gain. To balance the amplifier, a 0.22-μF capacitor and 49.9-Ω resistor to ground are inserted across  $R_{IT}$  on the alternate input.

The output is probed using a high-impedance differential probe across the 100-Ω resistor. The gain is referred to the amplifier output by adding back the 6-dB loss due to the voltage divider on the output.



**Figure 71. Frequency Response Test Circuit**

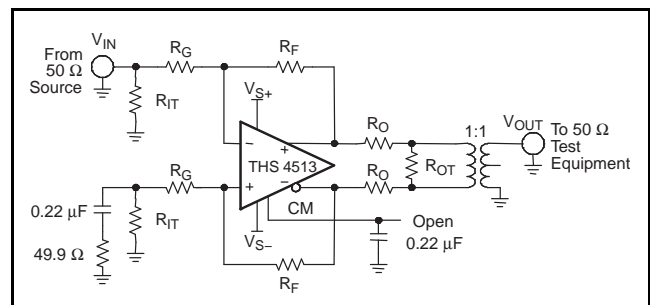
### Distortion and 1-dB Compression

The circuit shown in [Figure 72](#) is used to measure harmonic distortion, intermodulation distortion, and 1-dB compression point of the amplifier.

A signal generator is used as the signal source and the output is measured with a spectrum analyzer. The output impedance of the signal generator is 50 Ω.  $R_{IT}$  and  $R_G$  are chosen to impedance-match to 50 Ω, and to maintain the proper gain. To balance the amplifier, a 0.22-μF capacitor and 49.9-Ω resistor to ground are inserted across  $R_{IT}$  on the alternate input.

A low-pass filter is inserted in series with the input to reduce harmonics generated at the signal source. The level of the fundamental is measured, then a high-pass filter is inserted at the output to reduce the fundamental so that it does not generate distortion in the input of the spectrum analyzer.

The transformer used in the output to convert the signal from differential to single-ended is an ADT1-1WT. It limits the frequency response of the circuit so that measurements cannot be made below approximately 1 MHz.



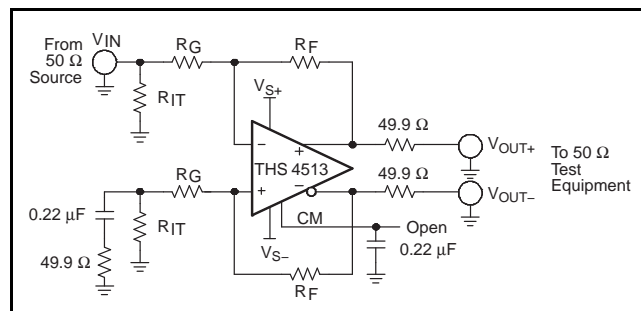
**Figure 72. Distortion Test Circuit**

The 1-dB compression point is measured with a spectrum analyzer with 50- $\Omega$  double termination or 100- $\Omega$  termination; see Table 2. The input power is increased until the output is 1 dB lower than expected. The number reported in the table data is the power delivered to the spectrum analyzer input. Add 3 dB to refer to the amplifier output.

### S-Parameter, Slew Rate, Transient Response, Settling Time, Output Impedance, Overdrive, Output Voltage, and Turn-On/Off Time

The circuit shown in Figure 73 is used to measure s-parameters, slew rate, transient response, settling time, output impedance, overdrive recovery, output voltage swing, and turn-on/turn-off times of the amplifier. For output impedance, the signal is injected at  $V_{OUT}$  with  $V_{IN}$  left open and the drop across the 49.9- $\Omega$  resistor is used to calculate the impedance seen looking into the amplifier output.

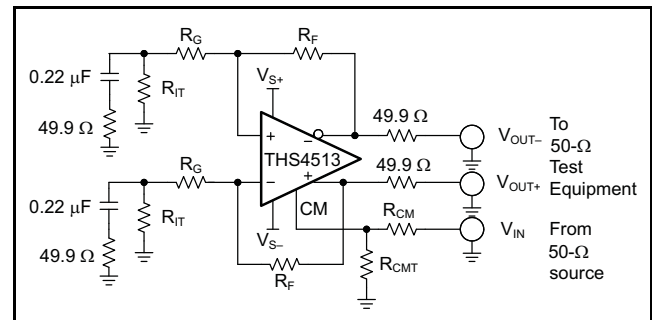
Because  $S_{21}$  is measured single-ended at the load with 50- $\Omega$  double termination, add 12 dB to refer to the amplifier's output as a differential signal.



**Figure 73. S-Parameter, SR, Transient Response, Settling Time,  $Z_O$ , Overdrive Recovery,  $V_{OUT}$  Swing, and Turn-On/Off Test Circuit**

### CM Input

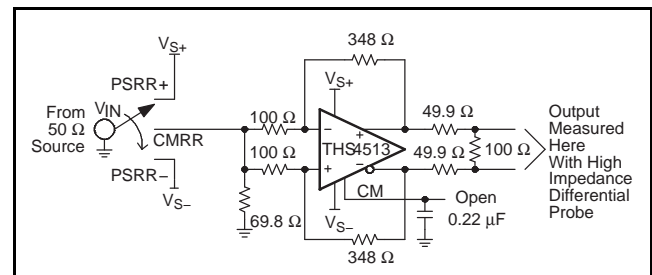
The circuit shown in Figure 74 is used to measure the frequency response and input impedance of the CM input. Frequency response is measured single-ended at  $V_{OUT+}$  or  $V_{OUT-}$  with the input injected at  $V_{IN}$ ,  $R_{CM} = 0 \Omega$  and  $R_{CMT} = 49.9 \Omega$ . The input impedance is measured with  $R_{CM} = 49.9 \Omega$  with  $R_{CMT} = \text{open}$ , and calculated by measuring the voltage drop across  $R_{CM}$  to determine the input current.



**Figure 74. CM Input Test Circuit**

### CMRR and PSRR

The circuit shown in Figure 75 is used to measure the CMRR and PSRR of  $V_{S+}$  and  $V_{S-}$ . The input is switched appropriately to match the test being performed.



**Figure 75. CMRR and PSRR Test Circuit**



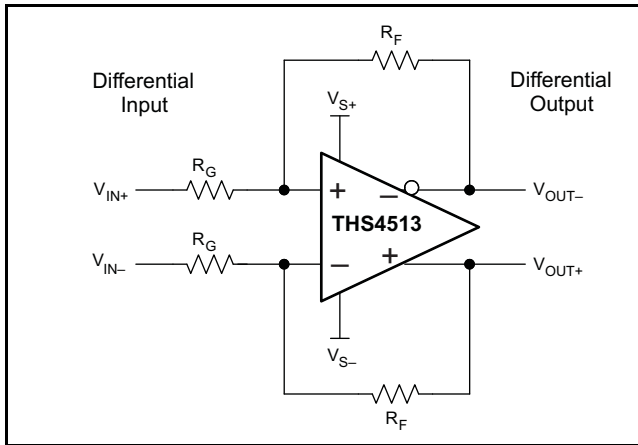
## APPLICATION INFORMATION

### APPLICATIONS

The following circuits show application information for the THS4513. For simplicity, power-supply decoupling capacitors are not shown in these diagrams. Please see the [THS4513 EVM](#) section for recommendations. For more detail on the use and operation of fully-differential op amps refer to the application report, *Fully-Differential Amplifiers* (SLOA054).

#### Differential Input to Differential Output Amplifier

The THS4513 is a fully-differential op amp, and can be used to amplify differential input signals to differential output signals. A basic block diagram of the circuit is shown in [Figure 76](#) (CM input not shown). The gain of the circuit is set by  $R_F$  divided by  $R_G$ .



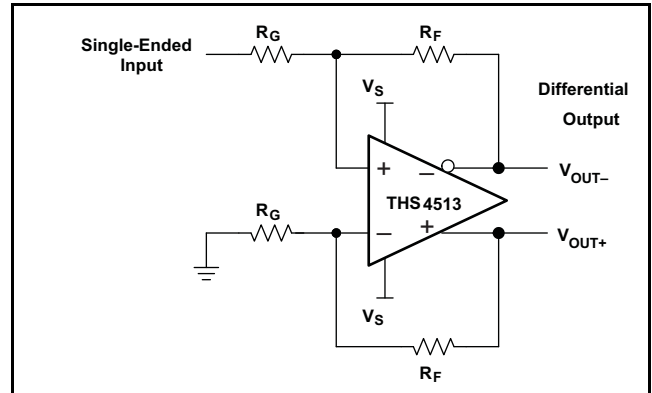
**Figure 76. Differential Input to Differential Output Amplifier**

Depending on the source and load, input and output termination can be accomplished by adding  $R_{IT}$  and  $R_O$ .

#### Single-Ended Input to Differential Output

#### Amplifier

The THS4513 can be used to amplify and convert single-ended input signals to differential output signals. A basic block diagram of the circuit is shown in [Figure 77](#) (CM input not shown). The gain of the circuit is again set by  $R_F$  divided by  $R_G$ .



**Figure 77. Single-Ended Input to Differential Output Amplifier**

#### Input Common-Mode Voltage Range

The input common-mode voltage of a fully differential op amp is the voltage at the '+' and '-' input pins of the op amp.

It is important to not violate the input common-mode voltage range ( $V_{ICR}$ ) of the op amp. Assuming the op amp is in linear operation the voltage across the input pins is only a few millivolts at most. So finding the voltage at one input pin will determine the input common-mode voltage of the op amp.

Treating the negative input as a summing node, the voltage is given by [Equation 1](#):

$$V_{IC} = \left( V_{OUT+} \times \frac{R_G}{R_G + R_F} \right) + \left( V_{IN-} \times \frac{R_F}{R_G + R_F} \right) \quad (1)$$

To determine the  $V_{ICR}$  of the op amp, the voltage at the negative input is evaluated at the extremes of  $V_{OUT+}$ .

As the gain of the op amp increases, the input common-mode voltage becomes closer and closer to the input common-mode voltage of the source.

## Setting the Output Common-Mode Voltage

The output common-mode voltage is set by the voltage at the CM pin(s). The internal common-mode control circuit maintains the output common-mode voltage within 3-mV offset (typ) from the set voltage, when set within 0.5 V of midsupply, with less than 4-mV differential offset voltage. If left unconnected, the common-mode set point is set to midsupply by internal circuitry, which may be over-driven from an external source. Figure 78 is representative of the CM input. The internal CM circuit has about 700 MHz of –3-dB bandwidth, which is required for best performance, but it is intended to be a dc bias input pin. Bypass capacitors are recommended on this pin to reduce noise at the output. The external current required to overdrive the internal resistor divider is given by Equation 2:

$$I_{EXT} = \frac{2V_{CM} - (V_{S+} - V_{S-})}{50 \text{ k}\Omega} \quad (2)$$

where  $V_{CM}$  is the voltage applied to the CM pin.

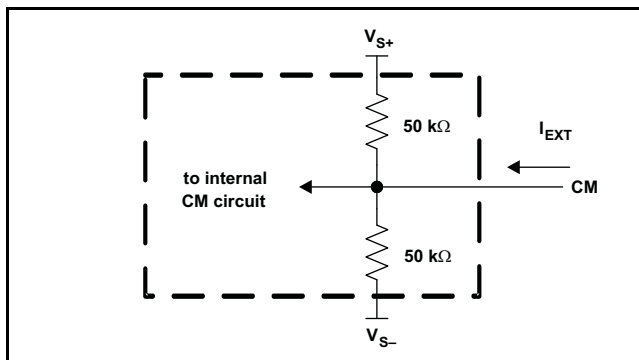


Figure 78. CM Input Circuit

## Single-Supply Operation (3 V to 5 V)

To facilitate testing with common lab equipment, the THS4513 EVM allows split-supply operation, and the characterization data presented in this data sheet were taken with split-supply power inputs. The device can easily be used with a single-supply power input without degrading the performance. Figure 79, Figure 80, and Figure 81 show dc and ac-coupled single-supply circuits with single-ended inputs. These configurations all allow the input and output common-mode voltage to be set to midsupply allowing for optimum performance. The information presented here can also be applied to differential input sources.

In Figure 79, the signal source is referenced to a voltage derived from the CM pin via a unity-gain wideband buffer such as the BUF602.  $V_{CM}$  is set to midsupply by THS4513 internal circuitry.  $R_T$  along with the input impedance of the amplifier provides input termination, which is also referenced to  $V_{CM}$ .

Note that  $R_S$  and  $R_T$  are added to the alternate input from the signal input to balance the amplifier. Alternately, one resistor can be used equal to the combined value  $R_G + R_S \parallel R_T$  on this input. This technique is also true of the circuits shown in Figure 80 and Figure 81.

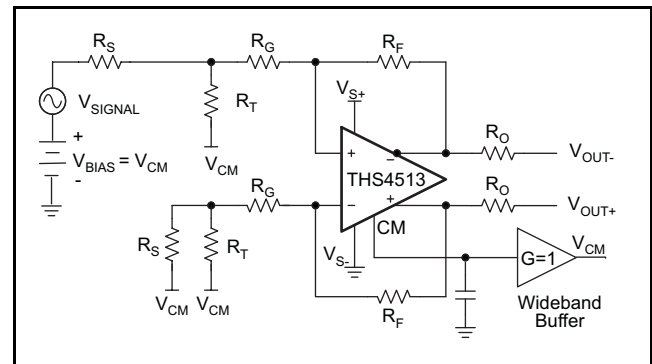


Figure 79. THS4513 DC-Coupled Single-Supply with Input Biased to  $V_{CM}$

In Figure 80, the source is referenced to ground and so is the input termination resistor.  $R_{PU}$  is added to the circuit to avoid violating the  $V_{ICR}$  of the op amp. The proper value of resistor to add can be calculated from Equation 3:

$$R_{PU} = \frac{(V_{IC} - V_{S+})}{V_{CM} \left( \frac{1}{R_F} \right) - V_{IC} \left( \frac{1}{R_{IN}} + \frac{1}{R_F} \right)} \quad (3)$$

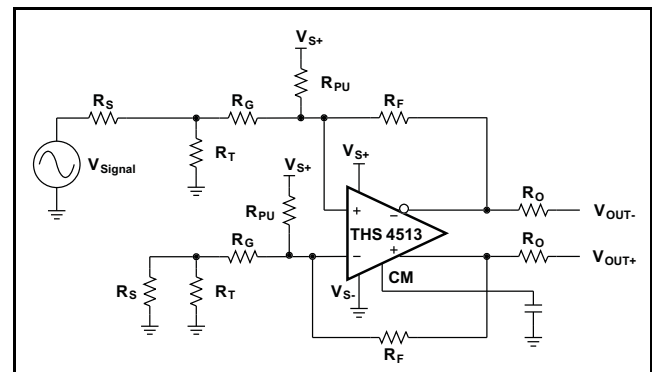


Figure 80. THS4513 DC-Coupled Single-Supply with  $R_{PU}$  Used to Set  $V_{IC}$

$V_{IC}$  is the desired input common-mode voltage,  $V_{CM} = CM$ , and  $R_{IN} = R_G + R_S \parallel R_T$ . To set to midsupply, make the value of  $R_{PU} = R_G + R_S \parallel R_T$ .

Table 3 is a modification of Table 1 to add the proper values with  $R_{PU}$  assuming a 50-Ω source impedance and setting the input and output common-mode voltage to midsupply.

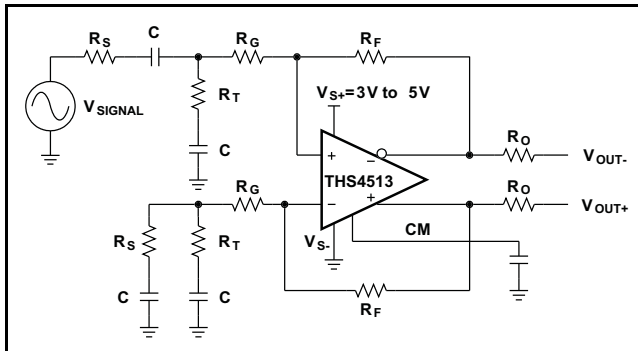
There are two drawbacks to this configuration. One is that it requires additional current from the power supply. Using the values shown for a gain of 0 dB requires 14 mA more current with 5-V supply, and 8.2 mA more current with 3-V supply.

The other drawback is that this configuration also increases the noise gain of the circuit. In the 10-dB gain case, noise gain increases by a factor of 1.5.

**Table 3.  $R_{PU}$  Values for Various Gains**

Gain	$R_F$	$R_G$	$R_{IT}$	$R_{PU}$
0 dB	348 Ω	340 Ω	56.2 Ω	365 Ω
6 dB	348 Ω	168 Ω	64.9 Ω	200 Ω

Figure 81 shows ac-coupling to the source. Using capacitors in series with the termination resistors allows the amplifier to self-bias both input and output to midsupply.

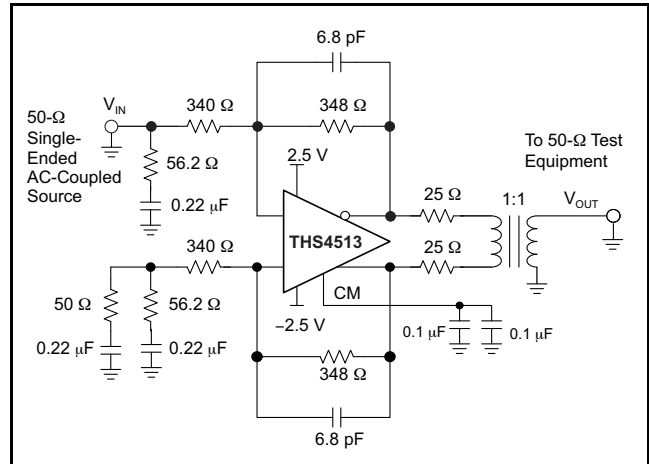


**Figure 81. THS4513 AC-Coupled Single-Supply**

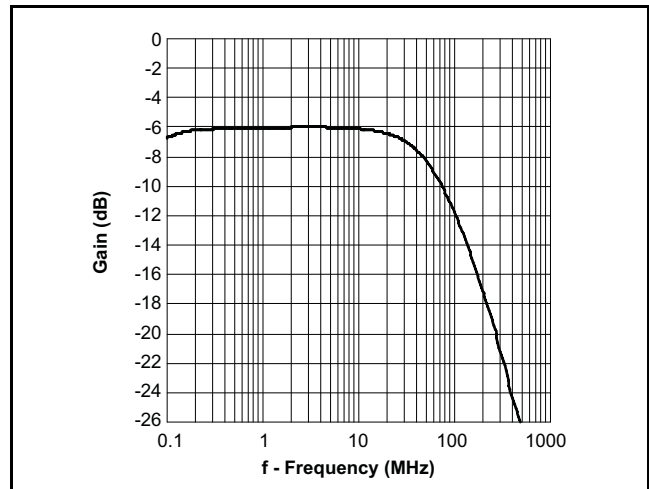
### Low-Pass Filter

One application for the THS4513 is as a unity-gain buffer with low-pass filtering. Figure 82 shows a circuit that is driven by an ac-coupled 50-Ω source. A 1:1 transformer converts the differential output of the THS4513 into a single-ended output capable of

driving 50-Ω test equipment. The circuit as shown has an overall gain of –6 dB due to the voltage divider on the device output, and has a roll-off frequency of approximately 60 MHz. The measured gain versus frequency response of the overall circuit is shown in Figure 83. The low-frequency roll-off is due to losses in the output transformer at those frequencies.



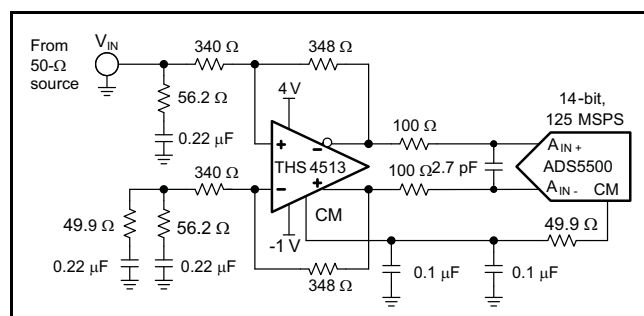
**Figure 82. 60-MHz Low-Pass Filter**



**Figure 83. Low-Pass Filter Measured Frequency Response**

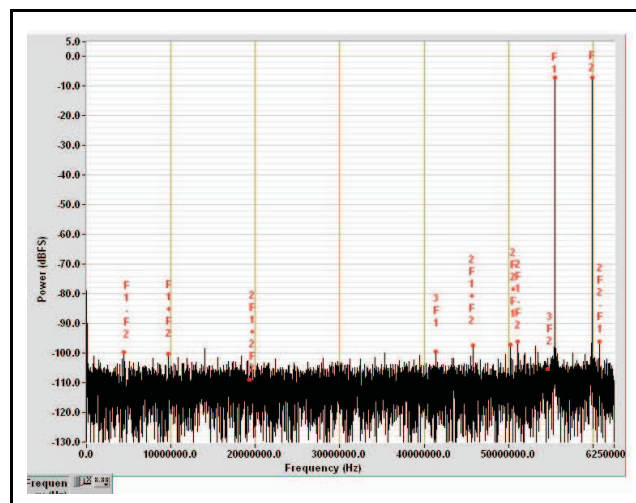
### THS4513 and ADS5500 Combined Performance

The THS4513 is designed to be a high-performance drive amplifier for high-performance data converters like the ADS5500 14-bit 125-MSPS ADC. **Figure 84** shows a circuit combining the two devices. The THS4513 amplifier circuit provides 10 dB of gain, converts the single-ended input to differential, and sets the proper input common-mode voltage to the ADS5500. The 100- $\Omega$  resistors and 2.7-pF capacitor between the THS4513 outputs and ADS5500 inputs along with the input capacitance of the ADS5500 limit the bandwidth of the signal to 115 MHz ( $-3$  dB). For testing, a signal generator is used for the signal source. The generator is an ac-coupled 50- $\Omega$  source. A band-pass filter is inserted in series with the input to reduce harmonics and noise from the signal source. Input termination is accomplished via the 69.8- $\Omega$  resistor and 0.22- $\mu$ F capacitor to ground in conjunction with the input impedance of the amplifier circuit. A 0.22- $\mu$ F capacitor and 49.9- $\Omega$  resistor is inserted to ground across the 69.8- $\Omega$  resistor and 0.22- $\mu$ F capacitor on the alternate input to balance the circuit. Gain is a function of the source impedance, termination, and 348- $\Omega$  feedback resistor. Refer to **Table 3** for component values to set proper 50- $\Omega$  termination for other common gains. A split power supply of +4 V and  $-1$  V is used to set the input and output common-mode voltages to approximately midsupply while setting the input common-mode of the ADS5500 to the recommended +1.55 V. This configuration maintains maximum headroom on the internal transistors of the THS4513 to ensure optimum performance.



**Figure 84. THS4513 and ADS5500 Circuit**

**Figure 85** shows the two-tone FFT of the THS4513 and ADS5500 circuit with 65 MHz and 70 MHz input frequencies. The SFDR is 90 dBc.



**Figure 85. THS4513 and ADS5500 2-Tone FFT with 65-MHz and 70-MHz Inputs**

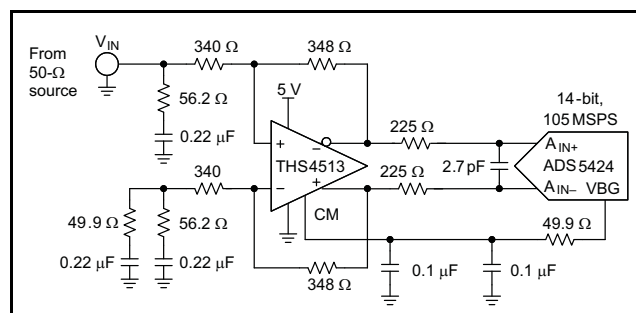
### THS4513 and ADS5424 Combined Performance

**Figure 86** shows the THS4513 driving the ADS5424 ADC.

As before, the THS4513 amplifier provides 10 dB of gain, converts the single-ended input to differential, and sets the proper input common-mode voltage to the ADS5424. Input termination and circuit testing is the same as described above for the THS4513 and ADS5500 circuit.

The 225- $\Omega$  resistors and 2.7-pF capacitor between the THS4513 outputs and ADS5424 inputs (along with the input capacitance of the ADC) limit the bandwidth of the signal to about 100 MHz ( $-3$  dB).

Since the ADS5424 recommended input common-mode voltage is 2.4 V, the THS4513 is operated from a single power-supply input with  $V_{S+} = 5$  V and  $V_{S-} = 0$  V (ground).



**Figure 86. THS4513 and ADS5424 Circuit**

## Layout Recommendations

It is recommended to follow the layout of the external components near the amplifier, ground plane construction, and power routing of the EVM as closely as possible. General guidelines are:

1. Signal routing should be direct and as short as possible into and out of the op amp circuit.
2. The feedback path should be short and direct; avoid vias.
3. Ground or power planes should be removed from directly under the amplifier input and output pins.
4. An output resistor is recommended on each output, as near to the output pin as possible.
5. Two 10- $\mu$ F and two 0.1- $\mu$ F power-supply decoupling capacitors should be placed as near to the power-supply pins as possible.
6. Two 0.1- $\mu$ F capacitors should be placed between the CM input pins and ground. This configuration limits noise coupled into the pins. One each should be placed to ground near pin 4 and pin 9.
7. It is recommended to split the ground plane on layer 2 (L2) as shown below and to use a solid ground on layer 3 (L3). A single-point connection should be used between each split section on L2 and L3.
8. A single-point connection to ground on L2 is recommended for the input termination resistors R1 and R2. This configuration should be applied to the input gain resistors if termination is not used.
9. The recommended printed circuit board (PCB) footprint for the THS4513 is shown in the Land Pattern of [Figure 88](#).

## PowerPAD™ DESIGN CONSIDERATIONS

The THS4513 is available in a thermally-enhanced PowerPAD family of packages. These packages are constructed using a downset leadframe on which the die is mounted (see [Figure 87a](#) and [Figure 87b](#)). This arrangement results in the lead frame being exposed

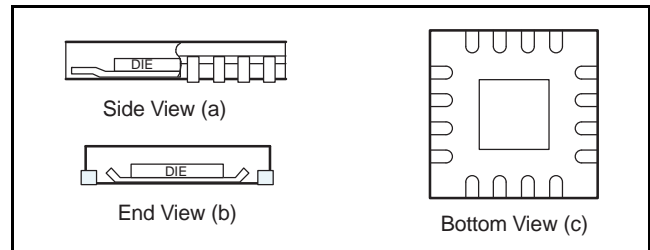
as a thermal pad on the underside of the package (see [Figure 87c](#)). Because this thermal pad has direct thermal contact with the die, excellent thermal performance can be achieved by providing a good thermal path away from the thermal pad.

Note that the THS4513 has no electrical connection between the PowerPAD and circuitry on the die. Connecting the PowerPAD to any potential voltage between  $V_{S+}$  and  $V_{S-}$  is acceptable. It is most important that it be connected for maximum heat dissipation.

The PowerPAD package allows both assembly and thermal management in one manufacturing operation.

During the surface-mount solder operation (when the leads are being soldered), the thermal pad can also be soldered to a copper area underneath the package. Through the use of thermal paths within this copper area, heat can be conducted away from the package into either a ground plane or other heat dissipating device.

The PowerPAD package represents a breakthrough in combining the small area and ease of assembly of surface-mount with the previously awkward mechanical methods of heatsinking.

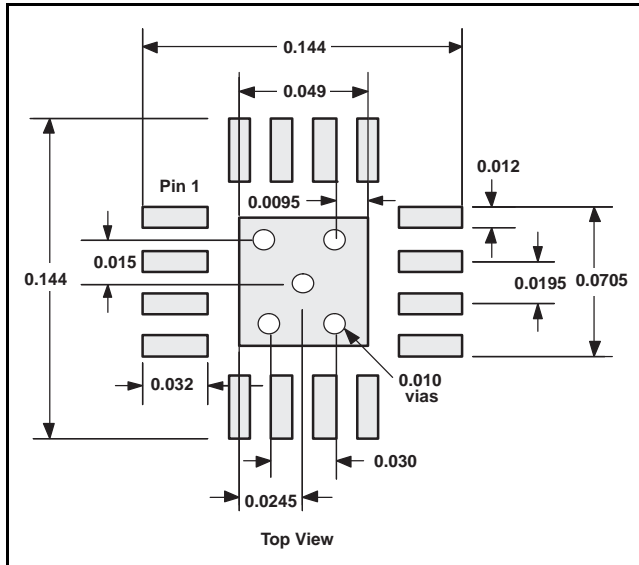


**Figure 87. Views of Thermally-Enhanced Package**



## PowerPAD PCB LAYOUT CONSIDERATIONS

Although there are many ways to properly heatsink the PowerPAD package, the following steps illustrate the recommended approach.



**Figure 88. PowerPAD PCB Etch and Via Pattern**

1. Prepare the PCB with a top side etch pattern as shown in [Figure 88](#). There should be etch for the leads as well as etch for the thermal pad.
2. Place five holes in the area of the thermal pad. The holes should be 13 mils (0.013 in, 0.33 mm) in diameter. Keep them small so that solder wicking through the holes is not a problem during reflow.
3. Additional vias may be placed anywhere along the thermal plane outside of the thermal pad area. They help dissipate the heat generated by the IC. These additional vias may be larger than the 13-mil diameter vias directly under the thermal pad. They can be larger because they are not in the thermal pad area to be soldered, so that wicking is not a problem.
4. Connect all holes to the internal ground plane.
5. When connecting these holes to the ground plane, **do not** use the typical web or spoke via connection methodology. Web connections have a high thermal resistance connection that is

useful for slowing the heat transfer during soldering operations. This resistance makes the soldering of vias that have plane connections easier. In this application, however, low thermal resistance is desired for the most efficient heat transfer. Therefore, the holes under the IC PowerPAD package should make the connection to the internal ground plane, with a complete connection around the entire circumference of the plated-through hole.

6. The top-side solder mask should leave the terminals of the package and the thermal pad area with its five holes exposed. The bottom-side solder mask should cover the five holes of the thermal pad area. This configuration prevents solder from being pulled away from the thermal pad area during the reflow process.
7. Apply solder paste to the exposed thermal pad area and all of the IC terminals.
8. With these preparatory steps in place, the IC is simply placed in position and run through the solder reflow operation as any standard surface-mount component. This process results in a part that is properly installed.

The next consideration is the package constraints. The two sources of heat within an amplifier are quiescent power and output power. The designer should never forget about the quiescent heat generated within the device, especially multi-amplifier devices. Because these devices have linear output stages (Class AB), most of the heat dissipation is at low output voltages with high output currents.

The other key factor when dealing with power dissipation is how the devices are mounted on the PCB. The PowerPAD devices are extremely useful for heat dissipation. But the device should always be soldered to a copper plane to fully use the heat dissipation properties of the PowerPAD. The SOIC package, on the other hand, is highly dependent on how it is mounted on the PCB. As more trace and copper area is placed around the device,  $\theta_{JA}$  decreases and the heat dissipation capability increases. For a single package, the sum of the RMS output currents and voltages should be used to choose the proper package.

## THS4513 EVM

Figure 89 is the THS4513 EVAL1 EVM schematic; layers 1 through 4 of the PCB are shown Figure 91, and Table 4 is the bill of materials for the EVM as supplied from TI.

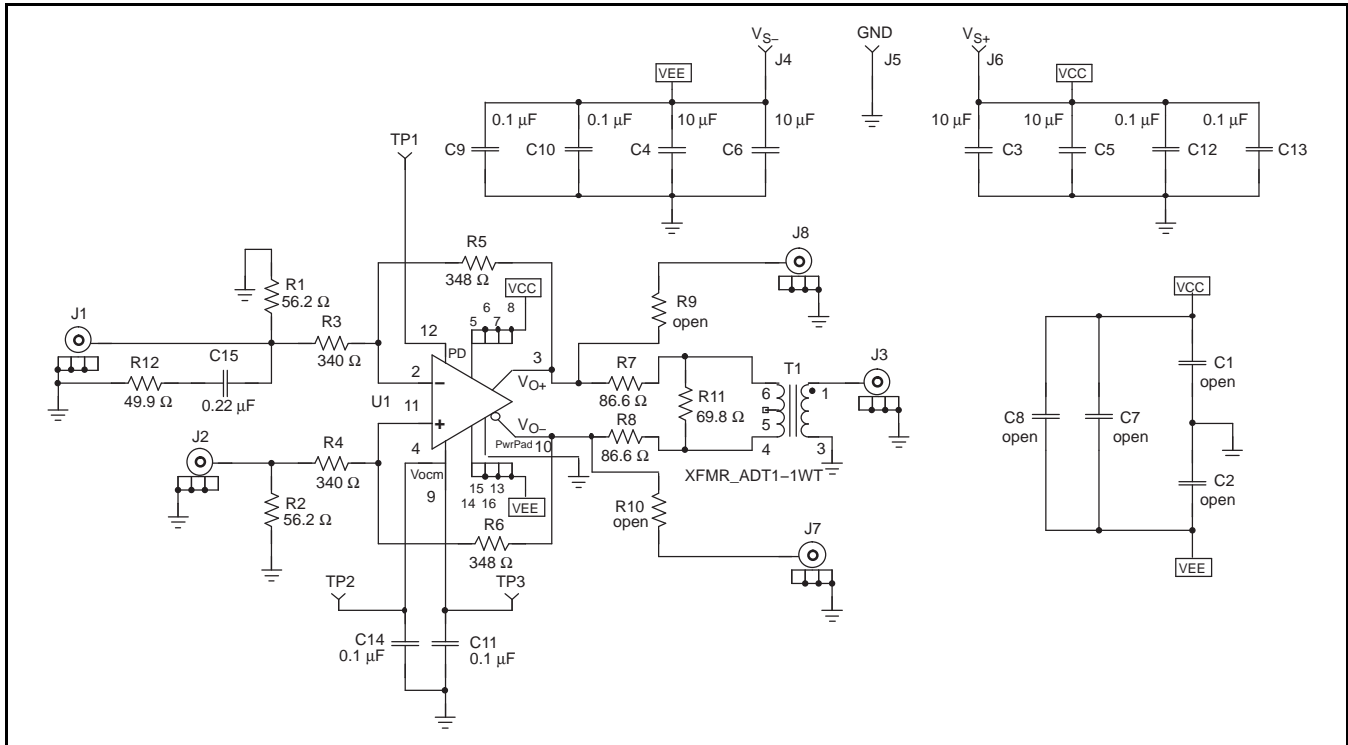


Figure 89. THS4513 EVAL1 EVM Schematic

Figure 90.

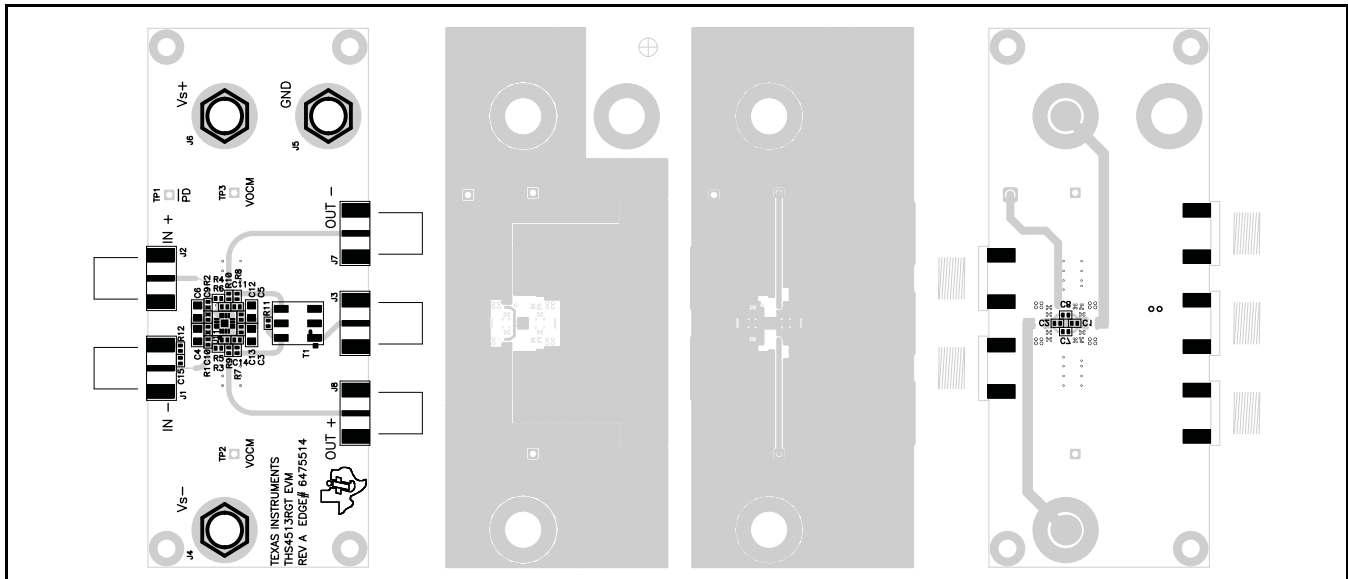


Figure 91. THS4513 EVAL1 EVM Layer 1 through Layer 4

**Table 4. THS4513 EVAL1 EVM Bill of Materials**

ITEM	DESCRIPTION	SMD SIZE	REFERENCE DESIGNATOR	PCB QTY	MANUFACTURER PART NUMBER
1	CAP, 10.0 $\mu$ F, Ceramic, X5R, 6.3 V	0805	C3, C4, C5, C6	4	(AVX) 08056D106KAT2A
2	CAP, 0.1 $\mu$ F, Ceramic, X5R, 10 V	0402	C9, C10, C11, C12, C13, C14	6	(AVX) 0402ZD104KAT2A
3	CAP, 0.22 $\mu$ F, Ceramic, X5R, 6.3 V	0402	C15	1	(AVX) 04026D224KAT2A
4	OPEN	0402	C1, C2, C7, C8	4	
5	OPEN	0402	R9, R10	2	
6	Resistor, 49.9 $\Omega$ , 1/16 W, 1%	0402	R12	1	(KOA) RK73H1ETTP49R9F
7	Resistor, 56.2 $\Omega$ , 1/16 W, 1%	0402	R1, R2	2	(KOA) RK73H1ETTP56R2F
8	Resistor, 69.8 $\Omega$ , 1/16 W, 1%	0402	R11	1	(KOA) RK73H1ETTP69R8F
9	Resistor, 86.6 $\Omega$ , 1/16 W, 1%	0402	R7, R8	2	(KOA) RK73H1ETTP86R6F
10	Resistor, 340 $\Omega$ , 1/16 W, 1%	0402	R3, R4	2	(KOA) RK73H1ETTP3400F
11	Resistor, 348 $\Omega$ , 1/16 W, 1%	0402	R5, R6	2	(KOA) RK73H1ETTP3480F
12	Transformer, RF		T1	1	(MINI-CIRCUITS) ADT1-1WT
13	Jack, banana receptance, 0.25" diameter hole		J4, J5, J6	3	(HH SMITH) 101
14	OPEN		J1, J7, J8	3	
15	Connector, edge, SMA PCB Jack		J2, J3	2	(JOHNSON) 142-0701-801
16	Test point, Red		TP1, TP2, TP3	3	(KEYSTONE) 5000
17	IC, THS4513		U1	1	(TI) THS4513RGT
18	Standoff, 4-40 HEX, 0.625" length			4	(KEYSTONE) 1808
19	SCREW, PHILLIPS, 4-40, 0.250"			4	SHR-0440-016-SN
20	Printed circuit board			1	(TI) EDGE# 6475514



## REVISION HISTORY

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

### Changes from Revision D (September 2009) to Revision E Page

- Changed  $R_G$  and  $R_{IT}$  values in [Table 1](#) ..... 23

### Changes from Revision C (May 2008) to Revision D Page

- Changed title of *Typical Characteristics:  $V_{S+} - V_{S-} = 5\text{ V}$*  ..... 8
- Deleted conditions from *Typical Characteristics:  $V_{S+} - V_{S-} = 5\text{ V}$*  table of graphs ..... 8
- Changed title of *Typical Characteristics:  $V_{S+} - V_{S-} = 3\text{ V}$*  ..... 16
- Deleted conditions from *Typical Characteristics:  $V_{S+} - V_{S-} = 3\text{ V}$*  table of graphs ..... 16
- Changed item 9 of the *Layout Recommendations* ..... 29
- Added the *PowerPAD Design Considerations* section ..... 29
- Added the *PowerPAD PCB Layout Considerations* section ..... 30
- Moved [Figure 88](#) and associated sentence to beginning of *PowerPAD PCB Layout Considerations* section ..... 30

### Changes from Revision B (November 2006) to Revision C Page

- Updated document format ..... 1
- Added [Related Products](#) table ..... 1
- Added footnote 1 to [Absolute Maximum Ratings](#) table ..... 2
- Added V (volts) to unit column of ESD ratings rows in [Absolute Maximum Ratings](#) table ..... 2
- Changed  $V_{S+} - V_{S-} = 5\text{ V}$  *Input* specifications from 1.75 V typ (common-mode input range high) to 1.4 V typ; -1.75 V (common-mode input range low) to -1.4 V; 1.67 M $\Omega$  || 1.32 pF (differential input impedance) to 1.3 M $\Omega$  || 1.8 pF; 1.2 M $\Omega$  || 1.45 pF (common-mode input impedance) to 1.0 M $\Omega$  || 2.3 pF ..... 3
- Added V (volts) to unit column of second *differential output voltage swing* row in *Output* section of  $V_{S+} - V_{S-} = 5\text{ V}$  specifications ..... 3
- Changed  $V_{S+} - V_{S-} = 3\text{ V}$  *Input* specifications from 0.75 V typ (common-mode input range high) to 0.4 V typ; -0.75 V (common-mode input range low) to -0.4 V ..... 5
- Added 1.3 M $\Omega$  || 1.8 pF (differential input impedance); 1.0 M $\Omega$  || 2.3 pF (common-mode input impedance) to  $V_{S+} - V_{S-} = 3\text{ V}$  *Input* specifications ..... 5
- Changed y-axis of [Figure 11](#) to match rest of curves ..... 10
- Changed y-axis of [Figure 12](#) to match rest of curves ..... 10
- Added 1.0 at end of x-axis in [Figure 23](#) ..... 12
- Changed last number in x-axis of [Figure 46](#) from 100 to 1000 ..... 17
- Changed last number in y-axis of [Figure 53](#) from 90 to 35 ..... 19

## PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish	MSL Peak Temp (3)	Op Temp (°C)	Top-Side Markings (4)	Samples
THS4513RGTR	ACTIVE	QFN	RGT	16	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	4513	<a href="#">Samples</a>
THS4513RGTRG4	ACTIVE	QFN	RGT	16	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	4513	<a href="#">Samples</a>
THS4513RGTT	ACTIVE	QFN	RGT	16	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	4513	<a href="#">Samples</a>
THS4513RGTTG4	ACTIVE	QFN	RGT	16	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	4513	<a href="#">Samples</a>

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSELETE:** TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check <http://www.ti.com/productcontent> for the latest availability information and additional product content details.

**TBD:** The Pb-Free/Green conversion plan has not been defined.

**Pb-Free (RoHS):** TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

**Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

**Green (RoHS & no Sb/Br):** TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) Multiple Top-Side Markings will be inside parentheses. Only one Top-Side Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Top-Side Marking for that device.

**Important Information and Disclaimer:** The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

**OTHER QUALIFIED VERSIONS OF THS4513 :**

- Space: [THS4513-SP](#)

## NOTE: Qualified Version Definitions:

- Space - Radiation tolerant, ceramic packaging and qualified for use in Space-based application

**TAPE AND REEL INFORMATION**


\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
THS4513RGTR	QFN	RGT	16	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2
THS4513RGTT	QFN	RGT	16	250	180.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2

## TAPE AND REEL BOX DIMENSIONS

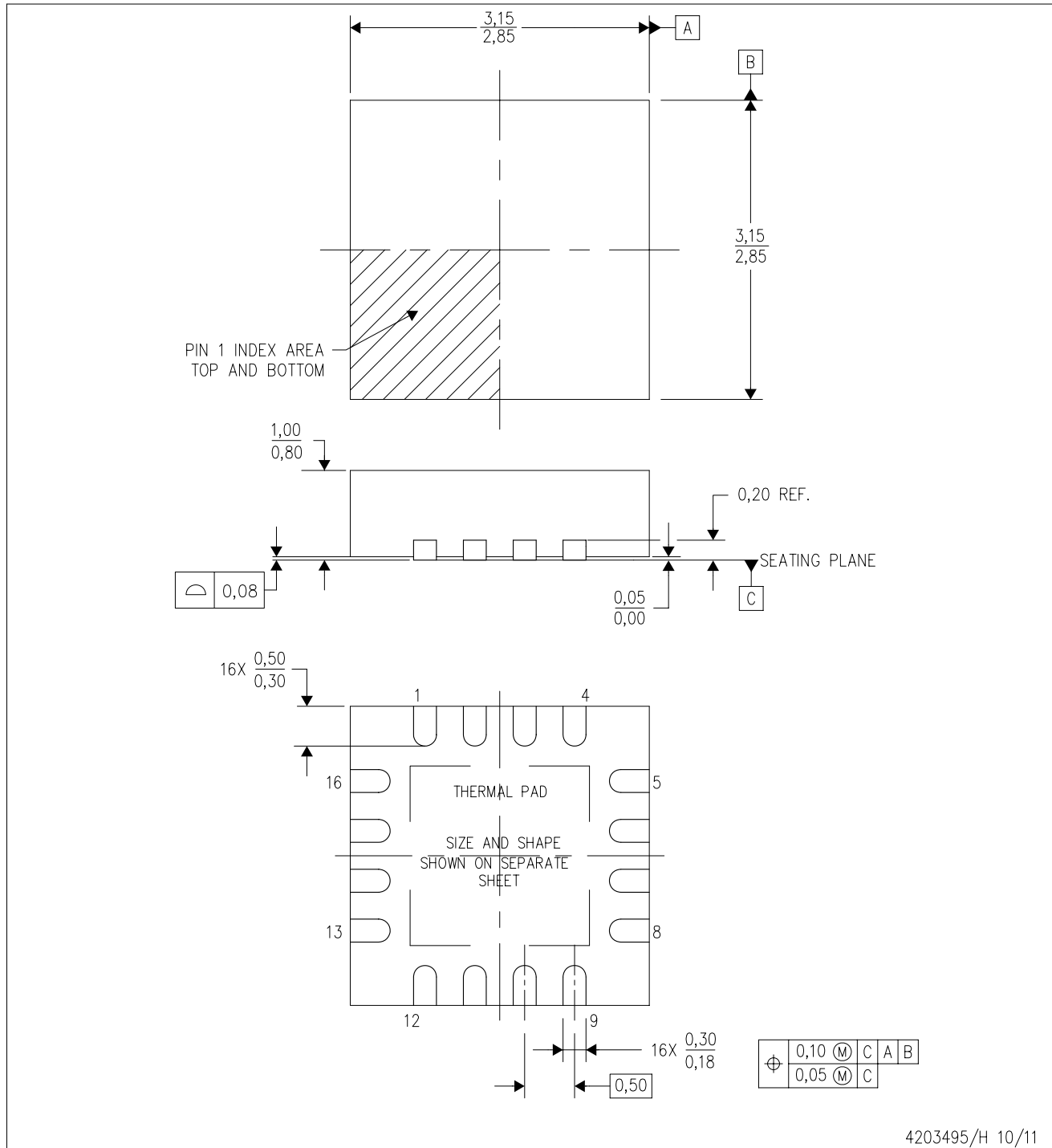


\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
THS4513RGTR	QFN	RGT	16	3000	367.0	367.0	35.0
THS4513RGTT	QFN	RGT	16	250	210.0	185.0	35.0

RGT (S-PVQFN-N16)

PLASTIC QUAD FLATPACK NO-LEAD



4203495/H 10/11

- NOTES:
- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.
  - B. This drawing is subject to change without notice.
  - C. Quad Flatpack, No-leads (QFN) package configuration.
  - D. The package thermal pad must be soldered to the board for thermal and mechanical performance.
  - E. See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions.
  - F. Falls within JEDEC MO-220.

## THERMAL PAD MECHANICAL DATA

RGT (S-PVQFN-N16)

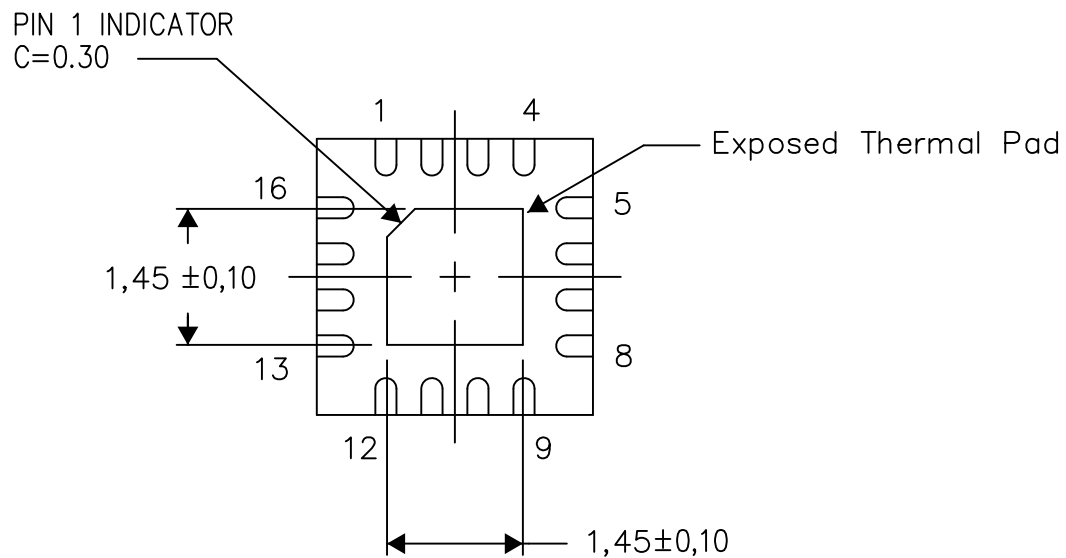
PLASTIC QUAD FLATPACK NO-LEAD

### THERMAL INFORMATION

This package incorporates an exposed thermal pad that is designed to be attached directly to an external heatsink. The thermal pad must be soldered directly to the printed circuit board (PCB). After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For information on the Quad Flatpack No-Lead (QFN) package and its advantages, refer to Application Report, QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271. This document is available at [www.ti.com](http://www.ti.com).

The exposed thermal pad dimensions for this package are shown in the following illustration.



Bottom View

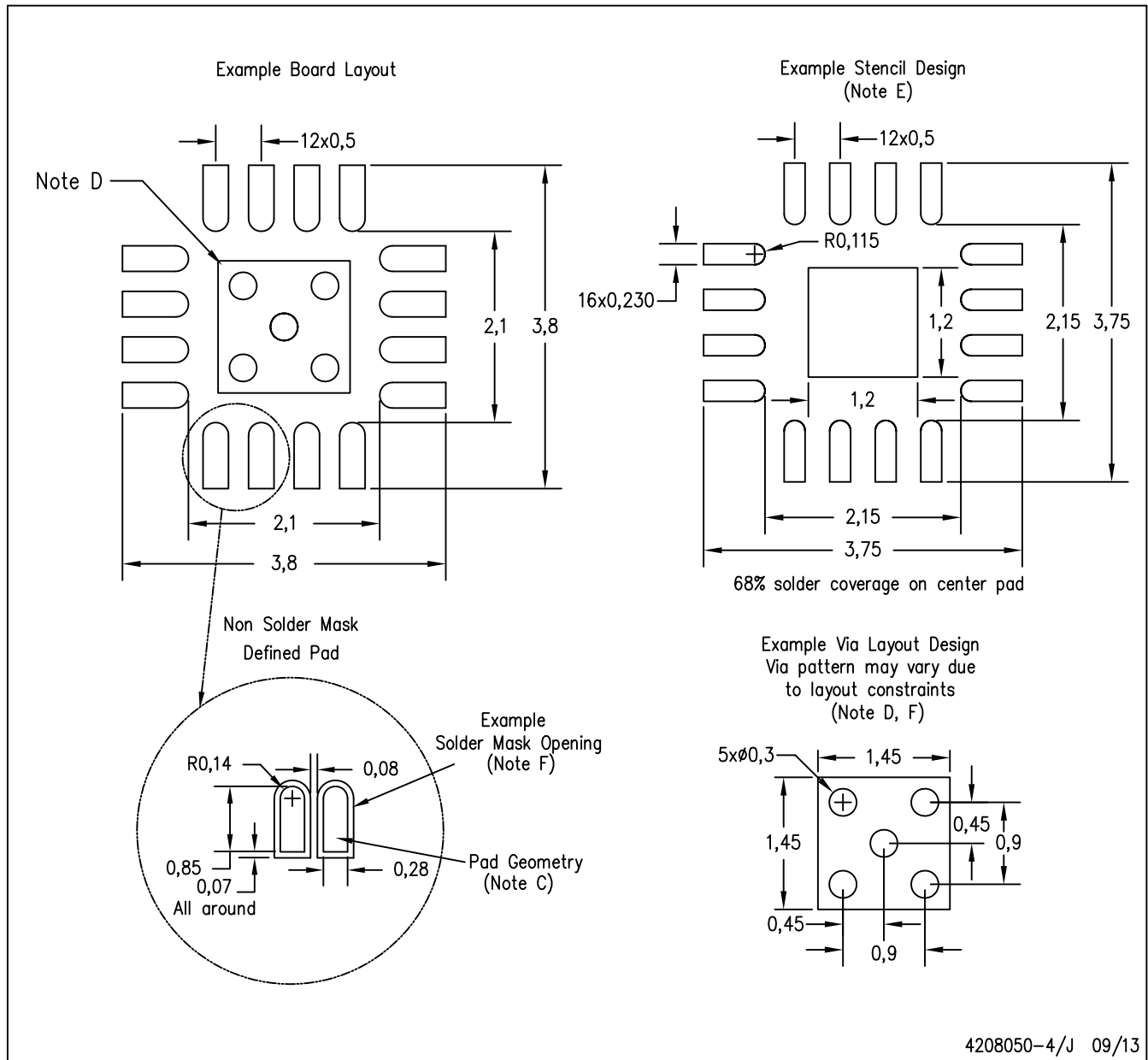
Exposed Thermal Pad Dimensions

4206349-2/U 09/13

NOTE: All linear dimensions are in millimeters

RGT (S-PVQFN-N16)

PLASTIC QUAD FLATPACK NO-LEAD



- NOTES:
- All linear dimensions are in millimeters.
  - This drawing is subject to change without notice.
  - Publication IPC-7351 is recommended for alternate designs.
  - This package is designed to be soldered to a thermal pad on the board. Refer to Application Note, QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at [www.ti.com](http://www.ti.com) <<http://www.ti.com>>.
  - Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
  - Customers should contact their board fabrication site for minimum solder mask web tolerances between signal pads.



## IMPORTANT NOTICE

Texas Instruments Incorporated and its subsidiaries (TI) reserve the right to make corrections, enhancements, improvements and other changes to its semiconductor products and services per JESD46, latest issue, and to discontinue any product or service per JESD48, latest issue. Buyers should obtain the latest relevant information before placing orders and should verify that such information is current and complete. All semiconductor products (also referred to herein as "components") are sold subject to TI's terms and conditions of sale supplied at the time of order acknowledgment.

TI warrants performance of its components to the specifications applicable at the time of sale, in accordance with the warranty in TI's terms and conditions of sale of semiconductor products. Testing and other quality control techniques are used to the extent TI deems necessary to support this warranty. Except where mandated by applicable law, testing of all parameters of each component is not necessarily performed.

TI assumes no liability for applications assistance or the design of Buyers' products. Buyers are responsible for their products and applications using TI components. To minimize the risks associated with Buyers' products and applications, Buyers should provide adequate design and operating safeguards.

TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right relating to any combination, machine, or process in which TI components or services are used. Information published by TI regarding third-party products or services does not constitute a license to use such products or services or a warranty or endorsement thereof. Use of such information may require a license from a third party under the patents or other intellectual property of the third party, or a license from TI under the patents or other intellectual property of TI.

Reproduction of significant portions of TI information in TI data books or data sheets is permissible only if reproduction is without alteration and is accompanied by all associated warranties, conditions, limitations, and notices. TI is not responsible or liable for such altered documentation. Information of third parties may be subject to additional restrictions.

Resale of TI components or services with statements different from or beyond the parameters stated by TI for that component or service voids all express and any implied warranties for the associated TI component or service and is an unfair and deceptive business practice. TI is not responsible or liable for any such statements.

Buyer acknowledges and agrees that it is solely responsible for compliance with all legal, regulatory and safety-related requirements concerning its products, and any use of TI components in its applications, notwithstanding any applications-related information or support that may be provided by TI. Buyer represents and agrees that it has all the necessary expertise to create and implement safeguards which anticipate dangerous consequences of failures, monitor failures and their consequences, lessen the likelihood of failures that might cause harm and take appropriate remedial actions. Buyer will fully indemnify TI and its representatives against any damages arising out of the use of any TI components in safety-critical applications.

In some cases, TI components may be promoted specifically to facilitate safety-related applications. With such components, TI's goal is to help enable customers to design and create their own end-product solutions that meet applicable functional safety standards and requirements. Nonetheless, such components are subject to these terms.

No TI components are authorized for use in FDA Class III (or similar life-critical medical equipment) unless authorized officers of the parties have executed a special agreement specifically governing such use.

Only those TI components which TI has specifically designated as military grade or "enhanced plastic" are designed and intended for use in military/aerospace applications or environments. Buyer acknowledges and agrees that any military or aerospace use of TI components which have **not** been so designated is solely at the Buyer's risk, and that Buyer is solely responsible for compliance with all legal and regulatory requirements in connection with such use.

TI has specifically designated certain components as meeting ISO/TS16949 requirements, mainly for automotive use. In any case of use of non-designated products, TI will not be responsible for any failure to meet ISO/TS16949.

### Products

Audio	<a href="http://www.ti.com/audio">www.ti.com/audio</a>
Amplifiers	<a href="http://amplifier.ti.com">amplifier.ti.com</a>
Data Converters	<a href="http://dataconverter.ti.com">dataconverter.ti.com</a>
DLP® Products	<a href="http://www.dlp.com">www.dlp.com</a>
DSP	<a href="http://dsp.ti.com">dsp.ti.com</a>
Clocks and Timers	<a href="http://www.ti.com/clocks">www.ti.com/clocks</a>
Interface	<a href="http://interface.ti.com">interface.ti.com</a>
Logic	<a href="http://logic.ti.com">logic.ti.com</a>
Power Mgmt	<a href="http://power.ti.com">power.ti.com</a>
Microcontrollers	<a href="http://microcontroller.ti.com">microcontroller.ti.com</a>
RFID	<a href="http://www.ti-rfid.com">www.ti-rfid.com</a>
OMAP Applications Processors	<a href="http://www.ti.com/omap">www.ti.com/omap</a>
Wireless Connectivity	<a href="http://www.ti.com/wirelessconnectivity">www.ti.com/wirelessconnectivity</a>

### Applications

Automotive and Transportation	<a href="http://www.ti.com/automotive">www.ti.com/automotive</a>
Communications and Telecom	<a href="http://www.ti.com/communications">www.ti.com/communications</a>
Computers and Peripherals	<a href="http://www.ti.com/computers">www.ti.com/computers</a>
Consumer Electronics	<a href="http://www.ti.com/consumer-apps">www.ti.com/consumer-apps</a>
Energy and Lighting	<a href="http://www.ti.com/energy">www.ti.com/energy</a>
Industrial	<a href="http://www.ti.com/industrial">www.ti.com/industrial</a>
Medical	<a href="http://www.ti.com/medical">www.ti.com/medical</a>
Security	<a href="http://www.ti.com/security">www.ti.com/security</a>
Space, Avionics and Defense	<a href="http://www.ti.com/space-avionics-defense">www.ti.com/space-avionics-defense</a>
Video and Imaging	<a href="http://www.ti.com/video">www.ti.com/video</a>

### TI E2E Community

[e2e.ti.com](http://e2e.ti.com)